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LP8556

参考資料

JAJSEF5L-JULY 2012-REVISED MAY 2019

Reference

E Design

# LP8556 タブレット向け高効率 LED バックライト・ドライバ

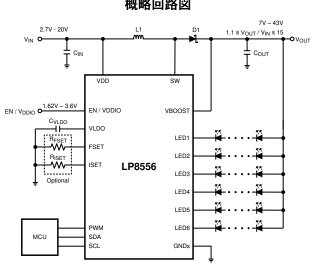
Technical

Documents

#### 特長 1

- 0.19Ωのパワー MOSFET を内蔵し、3 つのス イッチング周波数オプション (312kHz、625kHz、 1250kHz) に対応する、高効率 DC/DC 昇圧コン バータ
- 2.7V~36Vの昇圧スイッチ入力電圧範囲により、 マルチセルのリチウムイオン・バッテリに対応 (VDD 入力範囲: 2.7V~20V)
- 7V~43Vの昇圧スイッチ出力電圧範囲により、1 チャネルあたり直列に最小3個、最大12個の WLED に対応
- チャネル数を構成可能 (1~6)
- チャネルごとに最大 50mA
- PWM/I<sup>2</sup>C による輝度制御
- 位相シフト PWM モードにより可聴ノイズを低減
- 適応型調光により LED 駆動の光効率が向上
- プログラム可能なエッジレート制御と拡散スペク トラム方式により、スイッチング・ノイズを最小 限に抑え、EMI 耐性も向上
- LED フォルト (短絡および開放) 検出、UVLO、 TSD、OCP、OVP (最大 6 つのスレッショルド・ オプション)
- 小型の 20 ピン、0.4mm ピッチの DSBGA パッ ケージと、24 ピン、0.5mm ピッチの WQFN パッ ケージで供給
- 2 アプリケーション

タブレットの LCD 用の LED バックライト



# 概略回路図

# 3 概要

Tools &

Software

LP8556は、非同期昇圧コンバータと6つの高精度電流シ ンクを備えた白色LEDドライバであり、PWM信号やI<sup>2</sup>C マスタによる制御が可能です。

Support &

Community

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この昇圧コンバータは、適応型出力電圧制御を採用して おり、LEDドライバ電圧を7V~43Vの範囲で最適なレベル に設定します。この機能により、あらゆる条件下で出力電 圧が必要最低限のレベルに調整されるため、消費電力を 最小限に抑えることができます。3つのスイッチング周波数 (312kHz、625kHz、1250kHz)での動作が可能であり、外 付け抵抗を使用して設定したり、EPROMにより事前設定 することができます。プログラミング可能なスルーレート制 御と拡散スペクトラム方式により、スイッチング・ノイズは最 小限に抑えられ、EMI耐性も向上します。

LED電流シンクは、最大15ビットのPWM調光分解能によ り設定可能です。独自の適応型調光モードにより、システ ムの消費電力を削減できます。また、位相シフトLED PWM調光により、可聴ノイズを低減し、昇圧出力コンデン サを小型化することもできます。

LP8556には、デバイスと外付け部品の安定した動作が確 保されるよう、多様なフォルト保護機能が搭載されていま す。具体的にいうと、入力低電圧誤動作防止(UVLO)、 サーマル・シャットダウン(TSD)、過電流保護(OCP)、最大 6レベルの過電圧保護(OVP)、LED開放/短絡検出に対応 しています。

LP8556は-30℃~+85℃の周囲温度範囲で動作し、省 スペース型の20ピンDSBGAおよび24ピンWQFNパッ ケージで供給されます。

製品情報(1)					
型番	パッケージ	本体サイズ			
	DSBGA (20) 2.401mm×1.74				
LP8556	WQFN (24)	4.00mm×4.00mm (公称值)			

(1) 提供されているすべてのパッケージについては、巻末の注文情報 を参照してください。



Page

Page

Page

# 目次

8.4

1	特長	
2	アプ	リケーション 1
3	概要	
4	改訂	履歴2
5	Devi	ce Options3
6	Pin	Configuration and Functions 4
7	Spe	cifications
	7.1	Absolute Maximum Ratings 6
	7.2	ESD Ratings 6
	7.3	Recommended Operating Conditions 6
	7.4	Thermal Information 7
	7.5	Electrical Characteristics7
	7.6	Electrical Characteristics — Boost Converter
	7.7	Electrical Characteristics — LED Driver 9
	7.8	Electrical Characteristics — PWM Interface
	7.9	Electrical Characteristics — Logic Interface 10
	7.10	I <sup>2</sup> C Serial Bus Timing Parameters (SDA, SCL) 10
	7.11	Typical Characteristics 11
8	Deta	iled Description 12
	8.1	Overview 12

	8.6	Register Maps	32
9	App	lication and Implementation	45
	9.1	Application Information	45
	9.2	Typical Application	47
10	Pow	er Supply Recommendations	51
11	Laye	out	51
	11.1	Layout Guidelines	51
	11.2	Layout Examples	52
12	デバ	イスおよびドキュメントのサポート	54
	12.1	ドキュメントの更新通知を受け取る方法	54
	12.2	コミュニティ・リソース	54
	12.3	商標	54
	12.4	静電気放電に関する注意事項	
	12.5	Glossary	54
13	メカニ	ニカル、パッケージ、および注文情報	54

8.2 Functional Block Diagram ..... 12 8.3 Feature Description...... 13

8.5 Programming...... 28

# 4 改訂履歴

Re	evision K (March 2019) から Revision L に変更	Page
•	Deleted 03H register from Table 9	32
•	Deleted 8.6.1.4 Identification section from the Register Bit Explanations	33

#### Revision J (January 2018) から Revision K に変更

•	Added separate ESD Rating for the WQFN package - changed from "±2000" to "±1000"
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#### Revision I (March 2016) から Revision J に変更

Added content in VBOOST_RANGE description of CFG9E     38
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## Revision H (December 2014) から Revision I に変更

•	Changed "25 mA" to "23 mA" - E00, E08 and E09 SQ rows, E09, E11 TME rows	3
•	Changed Handing Ratings table to ESD Ratings	6
	Added updated Thermal Information	
•	Changed "8" to "10" in PWMres row	. 9
•	Changed subtracted 1 from bit value of all Table 4 "f <sub>PWM</sub> [Hz] (Resolution)" entries	20
•	Changed subtracted 1 from bit value of all Table 5 "f <sub>PWM</sub> [Hz] (Resolution)" entries except 2402	21
•	Changed subtracted 1 from bit value of all Table 11 " <i>f</i> <sub>PWM</sub> [Hz] (Resolution)" entries	45
•	Changed "via EPROM" in Table 13 title to "With an External Resistor"	46
•	Changed subtracted 1 from bit values of all Table 13 "f <sub>PWM</sub> [Hz] (Resolution)" entries except 2402	46



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## Revision G (November 2013) から Revision H に変更

## Revision E (August 2013) から Revision G に変更

# 5 Device Options

ORDERABLE DEVICE <sup>(1)</sup>	PACKAGE TYPE	DEVICE OPTION	LED CHANNEL COUNT	MAXIMUM LED CURRENT	BOOST OUTPUT VOLTAGE RANGE	
LP8556SQ-E00/NOPB LP8556SQE-E00/NOPB LP8556SQX-E00/NOPB			5			
LP8556SQ-E08/NOPB LP8556SQE-E08/NOPB LP8556SQX-E08/NOPB	WQFN	"PWM Only" – Recommended for systems without an I <sup>2</sup> C master.	4	23 mA	16 V to 34.5 V	
LP8556SQ-E09/NOPB LP8556SQE-E09/NOPB LP8556SQX-E09/NOPB			6			
LP8556TME-E02/NOPB LP8556TMX-E02/NOPB		"PWM and $I^2C$ " - Recommended for systems with an $I^2C$ master.	6	25 mA	16 V to 30 V	
LP8556TME-E03/NOPB LP8556TMX-E03/NOPB		"PWM Only" – Recommended for systems without an I <sup>2</sup> C master.	5	20 mA	16 V to 34.5 V	
LP8556TME-E04/NOPB LP8556TMX-E04/NOPB			6	20 mA	16 V to 25 V	
LP8556TME-E05/NOPB LP8556TMX-E05/NOPB	DSBGA	"Non-programmed" – This option is for evaluation purposes only.	Can be programmed to any available.	25 mA	Can be programmed to any available.	
LP8556TME-E06/NOPB LP8556TMX-E06/NOPB			5	25 mA	16 V to 39 V	
LP8556TME-E07/NOPB LP8556TMX-E07/NOPB		"PWM Only" – Recommended for systems without an I <sup>2</sup> C master.	4	20 mA	12.88 V to 30 V	
LP8556TME-E09/NOPB LP8556TMX-E09/NOPB			6	23 mA	16 V to 34.5 V	
LP8556TME-E11/NOPB LP8556TMX-E11/NOPB		"PWM and $I^2C$ " - Recommended for systems with an $I^2C$ master.	3	23 mA	7 V to 21 V	

(1) For the most current package and ordering information, see the *Package Option Addendum* at the end of this document, or see the TI website at www.ti.com.



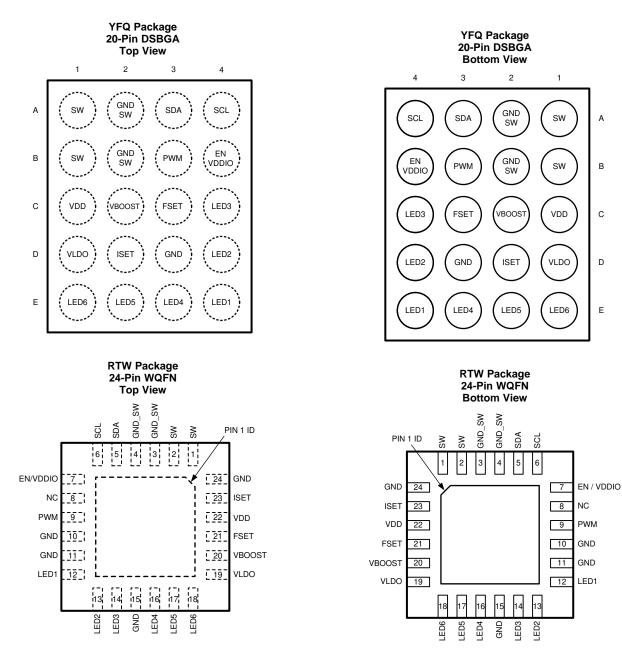
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Page

Page



# 6 Pin Configuration and Functions



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LP8556

	Pin Functions					
	PIN					
DSBGA	WQFN	NAME	ITPE."	DESCRIPTION		
A1, B1	1, 2	SW	А	A connection to the drain terminal of the integrated power MOSFET.		
A2, B2	3, 4	GND_SW	G	A connection to the source terminal of the integrated power MOSFET.		
A3	5	SDA	I/O	I <sup>2</sup> C data input/output pin		
A4	6	SCL	I	I <sup>2</sup> C clock input pin		
В3	9	PWM	I	PWM dimming input. Supply a 75-Hz to 25-kHz PWM signal to control dimming. This pin must be connected to GND if unused.		
B4	7	EN / VDDIO	Р	Dual-purpose pin serving both as a chip enable and as a power supply reference for PWM, SDA, and SCL inputs. Drive this pin with a logic gate capable of sourcing a minimum of 1 mA.		
C1	22	VDD	Р	Device power supply pin. Provide 2.7-V to 20-V supply to this pin. This pin is an input of the internal LDO regulator. The output of the internal LDO is what powers the device.		
C2	20	VBOOST	A	Boost converter output pin. The internal feedback (FB) and overvoltage protection (OVP) circuitry monitors the voltage on this pin. Connect the converter output capacitor bank close to this pin.		
СЗ	21	FSET	A	A connection for setting the boost frequency and PWM output dimming frequency by using an external resistor. Connect a resistor, $R_{FSET}$ , between this pin and the ground reference (see Table 5). This pin may be left floating if PWM_FSET_EN = 0 AND BOOST_FSET_EN = 0 (see Table 10).		
C4	14	LED3	А	LED driver - current sink terminal. If unused, it may be left floating.		
D1	19	VLDO	Р	Internal LDO output pin. Connect a capacitor, $C_{VLDO}$ , between this pin and the ground reference.		
D2	23	ISET	A	A connection for the LED current set resistor. Connect a resistor, $R_{ISET}$ , between this pin and the ground reference. This pin may be left floating if ISET_EN = 0 (see Table 10).		
D3	10, 11, 15, 24, DAP	GND	I	Ground pin.		
D4	13	LED2	А	LED driver - current sink pin. If unused, it may be left floating.		
E1	18	LED6	А	LED driver - current sink pin. If unused, it may be left floating.		
E2	17	LED5	А	LED driver - current sink pin. If unused, it may be left floating.		
E3	16	LED4	А	LED driver - current sink pin. If unused, it may be left floating.		
E4	12	LED1	А	LED driver - current sink pin. If unused, it may be left floating.		

No Connect pin.

(1) A: Analog Pin, G: Ground Pin, P: Power Pin, I: Digital Input Pin, I/O: Digital Input/Output Pin

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## 7 Specifications

## 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

	MIN	MAX	UNIT
V <sub>DD</sub>	-0.3	24	
Voltage on Logic Pins (SCL, SDA, PWM)	-0.3	6	
Voltage on Analog Pins (VLDO, EN / VDDIO)	-0.3	6	V
Voltage on Analog Pins (FSET, ISET)	-0.3	VLDO + 0.3	
V (LED1LED6, SW, VBOOST)	-0.3	50	
Junction Temperature (T <sub>J-MAX</sub> ) <sup>(3)</sup>		125	°C
Maximum Lead Temperature (Soldering)		260	°C
Storage temperature, T <sub>stg</sub>	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability, see the Electrical Characteristics tables.

(2) If Military/Aerospace specified devices are required, contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

(3) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be de-rated. Maximum ambient temperature (T<sub>A-MAX</sub>) is dependent on the maximum operating junction temperature (T<sub>J-MAX-OP</sub> = 125°C), the maximum power dissipation of the device in the application (P<sub>D-MAX</sub>), and the junction-to ambient thermal resistance of the part/package in the application (R<sub>θJA</sub>), as given by the following equation: T<sub>A-MAX</sub> = T<sub>J-MAX-OP</sub> - (R<sub>θJA</sub> × P<sub>D-MAX</sub>).

# 7.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001, DSBGA Package <sup>(1)</sup>	±2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001, WQFN Package <sup>(1)</sup>	±1000	V
	aloonargo	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

	MIN	MAX	UNIT
VDD	2.7	20	V
EN / VDDIO	1.62	3.6	V
V (LED1LED6, SW, VBOOST)	0	48	V
Junction temperature, T <sub>J</sub>	-30	125	°C
Ambient temperature, T <sub>A</sub>	-30	85	°C

(1) All voltages are with respect to the potential at the GND pins.

## 7.4 Thermal Information

		LP8	LP8556		
	THERMAL METRIC <sup>(1)</sup>	YFQ (DSBGA)	RTW (WQFN)	UNIT	
		20 PINS	24 PINS		
$R_{\thetaJA}$	Junction-to-ambient thermal resistance	66.2	35.0	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	0.5	32.2	°C/W	
$R_{\theta J B}$	Junction-to-board thermal resistance	15.1	13.7	°C/W	
ΨJT	Junction-to-top characterization parameter	1.9	0.3	°C/W	
Ψјв	Junction-to-board characterization parameter	15.0	13.8	°C/W	
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	3.3	°C/W	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report (SPRA953).

# 7.5 Electrical Characteristics

Unless otherwise specified: VDD = 12 V, EN / VDDIO = 1.8 V,  $T_A = 25^{\circ}C^{(1)(2)}$ 

	PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
V <sub>DDIO</sub>	Supply voltage for digital I/Os		1.62		3.6	V
V <sub>DD</sub>	Input voltage for the internal LDO		2.7		20	V
	Standby supply current	EN / VDDIO = 0 V, LDO disabled, -30°C $\leq T_A \leq 85°C$			1.6	μA
Normal mode supply current		LDO enabled, boost disabled		0.9	1.5	~
	Normal mode supply current	LDO enabled, boost enabled, no load		2.2	3.65	mA
4	Internal oscillator frequency		-4%		4%	
fosc	accuracy	–30°C ≤ T <sub>A</sub> ≤ 85°C	-7%		7%	
V		V <sub>DD</sub> ≥ 3.1 V	2.95	3.05	3.15	
V <sub>LDO</sub>	LDO output voltage	$2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.1 \text{ V}$	V <sub>DD</sub> – 0.05		V	
T <sub>TSD</sub>	Thermal shutdown threshold	See <sup>(3)</sup>		150		°C
T <sub>TSD_hyst</sub>	Thermal shutdown hysteresis	See		20		°C

(1) All voltages are with respect to the potential at the GND pins.

(2) (3) Minimum (MIN) and Maximum (MAX) limits are verified by design, test, or statistical analysis. Typical numbers are for information only.

Verified by design and not tested in production.

## 7.6 Electrical Characteristics — Boost Converter

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

	PARAMETER	TEST CON	DITIONS	MIN	TYP	MAX	UNIT
R <sub>DS_ON</sub>	Switch ON resistance	I <sub>SW</sub> = 0.5A			0.19		Ω
V <sub>BOOST_MIN</sub>	Boost minimum output voltage	VBOOST_RANGE = 0 VBOOST_RANGE = 1			7 16		V
		VBOOST_MAX = 100, VBOOST_MAX = 101, VBOOST_MAX = 101, VBOOST_MAX = 110, VBOOST_MAX = 111, VBOOST_MAX = 100, VBOOST_MAX =	/BOOST_RANGE = 0 /BOOST_RANGE = 0	19 24.0 28.0 32	21 25 30 34	22 27 32 37	V
V <sub>BOOST_MAX</sub>	Boost maximum output voltage	VBOOST_MAX = 010, VBOOST_RANGE = 1 VBOOST_MAX = 011, VBOOST_RANGE = 1 VBOOST_MAX = 100, VBOOST_RANGE = 1 VBOOST_MAX = 101, VBOOST_RANGE = 1 VBOOST_MAX = 110, VBOOST_RANGE = 1 VBOOST_MAX = 111, VBOOST_RANGE = 1		17.9 22.8 27.8 32.7 37.2 41.8	21 25 30 34.5 39 43	23.1 27.2 31.5 36.6 40.8 44.2	V
	V <sub>IN</sub> = 3 V, V <sub>OUT</sub> = 18 V		220				
ILOAD_MAX	Maximum continuous output load current	$V_{IN}$ = 3 V, $V_{OUT}$ = 24 V			160		mA
		V <sub>IN</sub> = 3 V, V <sub>OUT</sub> = 30 V			120		
	0	f <sub>SW</sub> = 625 kHz	f <sub>SW</sub> = 625 kHz			15	
V <sub>OUT</sub> /V <sub>IN</sub>	Conversion ratio <sup>(2)</sup>	f <sub>SW</sub> = 1250 kHz				12	
f <sub>SW</sub>	Switching frequency	BOOST_FREQ = 00 BOOST_FREQ = 01 BOOST_FREQ = 10		312 625 1250		kHz	
V <sub>OVP</sub>	Overvoltage protection voltage	VBOOST_RANGE = 1	V	BOOST + 1.6		V	
		UVLO_EN = 1					
V <sub>UVLO</sub>	V <sub>IN</sub> undervoltage lockout threshold	UVLO_TH = 0, falling UVLO_TH = 1, falling			2.5 5.2		V
<i>\</i> /	V hustonesia	V <sub>UVLO</sub> [rising]	$UVLO_TH = 0$		50		
V <sub>UVLO_hyst</sub>	V <sub>UVLO</sub> hysteresis	V <sub>UVLO</sub> [falling]	UVLO_TH = 1		100		mV
t <sub>PULSE</sub>	Switch minimum pulse width	No load			50		ns
t <sub>STARTUP</sub>	Start-up time	See <sup>(3)</sup>			8		ms
I <sub>SW LIM</sub>	SW pin current limit <sup>(4)</sup>	IBOOST_LIM_2X = 0	IBOOST_LIM = 00 IBOOST_LIM = 01 IBOOST_LIM = 10 IBOOST_LIM = 11	0.66 0.88 1.12 1.35	0.9 1.2 1.5 1.8	1.16 1.40 1.73 2.07	A
ON_LIN		IBOOST_LIM_2X = 1	IBOOST_LIM = 00 IBOOST_LIM = 01 IBOOST_LIM = 10		1.6 2.1 2.6		А
∆V <sub>SW</sub> / t <sub>off_on</sub>	SW pin slew rate during OFF to ON transition				3.7 5.3 7.5		V/ns
∆V <sub>SW</sub> / t <sub>on_off</sub>	SW pin slew rate during ON to OFF transition	EN_DRV3 = 0 AND EN EN_DRV3 = 0 AND EN EN_DRV3 = 1 AND EN	_DRV2 = 1		1.9 4.4 4.8		V/ns
$\Delta t_{ON}$ / $t_{SW}$	Peak-to-peak switch ON time deviation to SW period ratio (spread spectrum feature)	SSCLK_EN = 1			1%		

Minimum (MIN) and Maximum (MAX) limits are verified by design, test, or statistical analysis. Typical numbers are for information only. (1)

(2) Verified by design and not tested in production.

 (3) Start-up time is measured from the moment boost is activated until the V<sub>BOOST</sub> crosses 90% of its target value.
 (4) 1.8 A is the maximum I<sub>SW\_LIM</sub> supported with the DSBGA package. For applications requiring the I<sub>SW\_LIM</sub> to be greater than 1.8 A and up to 2.6 A, WQFN package should be considered.

## 7.7 Electrical Characteristics — LED Driver

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
ILED_LEAKAGE	Leakage current	Outputs LED1LED6, V <sub>OUT</sub> = 48 V		0.1	1	μA
I <sub>LED_MAX</sub>	Maximum sink current LED1LED6			50		mA
		Output current set to 23 mA	-3%	1%	3%	
I <sub>LED</sub>	LED current accuracy <sup>(2)</sup>	Output current set to 23 mA, $-30^{\circ}C \le T_A \le 85^{\circ}C$	-4%	1%	4%	
IMATCH	Matching	Output current set to 23 mA		0.5%		
	LED PWM output pulse duty cycle <sup>(3)</sup>	100 Hz < f <sub>PWM</sub> ≤ 200 Hz	0.02%		100%	
		200 Hz < f <sub>PWM</sub> ≤ 500 Hz	0.02%		100%	
		500 Hz < f <sub>PWM</sub> ≤ 1 kHz	0.02%		100%	
		1 kHz < f <sub>PWM</sub> ≤ 2 kHz	0.04%		100%	
PWM <sub>DUTY</sub>		2 kHz < f <sub>PWM</sub> ≤ 5 kHz	0.1%		100%	
		5 kHz < $f_{PWM} \le 10$ kHz	0.2%		100%	
		10 kHz < f <sub>PWM</sub> ≤ 20 kHz	0.4%		100%	
		20 kHz < f <sub>PWM</sub> ≤ 30 kHz	0.6%		100%	
		30 kHz < f <sub>PWM</sub> ≤ 39 kHz	0.8%		100%	
f <sub>LED</sub>	PWM output frequency	PWM_FREQ = 1111		38.5		kHz
V <sub>SAT</sub>	Saturation voltage <sup>(4)</sup>	Output current set to 23 mA		200		mV

(1) Minimum (MIN) and Maximum (MAX) limits are specified by design, test, or statistical analysis. Typical numbers are not verified, but do represent the most likely norm.

(2) Output Current Accuracy is the difference between the actual value of the output current and programmed value of this current. Matching is the maximum difference from the average. For the constant current sinks on the part (OUT1 to OUT6), the following are determined: the maximum output current (MAX), the minimum output current (MIN), and the average output current of all outputs (AVG). Two matching numbers are calculated: (MAX-AVG)/AVG and (AVG-MIN/AVG). The largest number of the two (worst case) is considered the matching figure. The typical specification provided is the most likely norm of the matching figure for all parts. Note that some manufacturers have different definitions in use.

(3) Verified by design and not tested in production.

(4) Saturation voltage is defined as the voltage when the LED current has dropped 10% from the value measured at 1 V.

#### 7.8 Electrical Characteristics — PWM Interface<sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f <sub>PWM</sub>	PWM frequency range <sup>(2)</sup>		75		25 000	Hz
t <sub>MIN_ON</sub>	Minimum pulse ON time			1		
t <sub>MIN_OFF</sub>	Minimum pulse OFF time			1		μS
t <sub>STARTUP</sub>	Turnon delay from standby to backlight on	PWM input active, VDDIO pin transitions from 0 V to 1.8 V		10		ms
t <sub>STBY</sub>	Turnoff delay	PWM input low time for turnoff		50		ms
PWM <sub>RES</sub>	PWM input resolution	$f_{\rm IN}$ < 9 kHz		10		bits

(1) Minimum (MIN) and Maximum (MAX) limits are specified by design, test, or statistical analysis. Typical numbers are for information only.

(2) Verified by design and not tested in production.



# 7.9 Electrical Characteristics — Logic Interface <sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
LOG	IC INPUTS (PWM, SDA, SCL	-)				
V <sub>IL</sub>	Input low level	$-30^{\circ}C \le T_A \le 85^{\circ}C$			0.3 × VDDIO	V
VIH	Input high level	$-30^{\circ}C \le T_A \le 85^{\circ}C$	0.7 × VDDIO			V
I <sub>I</sub>	Input current	$(V_{DDIO} = 0 \text{ V or } 3.6 \text{ V}), (V_I = 0 \text{ V or } 3.6 \text{ V}), -30^{\circ}\text{C} \le \text{T}_A \le 85^{\circ}\text{C}$	-1		1	μA
LOG	IC OUTPUTS (SDA)					
		I <sub>OUT</sub> = 3 mA (pull-up current)		0.3		
V <sub>OL</sub>	Output low level	$I_{OUT} = 3 \text{ mA} \text{ (pull-up current)}, -30^{\circ}\text{C} \le T_{A} \le 85^{\circ}\text{C}$		0.3	0.4	V
۱ <sub>L</sub>	Output leakage current	$V_{OUT} = 5 \text{ V}, -30^{\circ}\text{C} \le T_{A} \le 85^{\circ}\text{C}$	-1		1	μA

(1) Minimum (MIN) and Maximum (MAX) limits are specified by design, test, or statistical analysis. Typical numbers are for information only.

# 7.10 I<sup>2</sup>C Serial Bus Timing Parameters (SDA, SCL)<sup>(1)</sup>

		MIN	MAX	UNIT
f <sub>SCL</sub>	Clock frequency		400	kHz
1	Hold time (repeated) START condition	0.6		μs
2	Clock low time	1.3		μs
3	Clock high time	600		ns
4	Setup time for a repeated START condition	600		ns
5	Data hold time	50		ns
6	Data set-up time	100		ns
7	Rise time of SDA and SCL	20 + 0.1C <sub>b</sub>	300	ns
8	Fall time of SDA and SCL	15 + 0.1C <sub>b</sub>	300	ns
9	Setup time for STOP condition	600		ns
10	Bus-free time between a STOP and a START condition	1.3		μs
C <sub>b</sub>	Capacitive load parameter for each bus line load of 1 pF corresponds to 1 ns.	10	200	ns

(1) Verified by design and not tested in production.

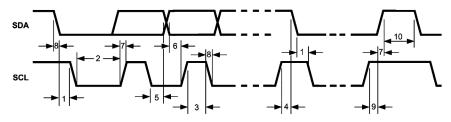
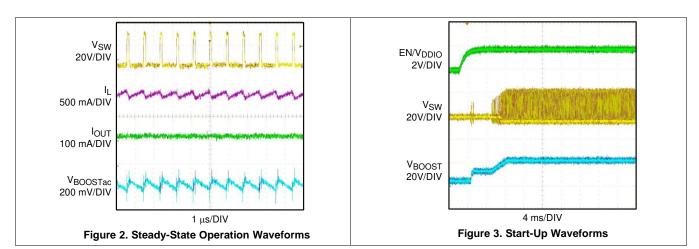


Figure 1. I<sup>2</sup>C-Compatible Timing



## 7.11 Typical Characteristics

Unless otherwise specified: V<sub>IN</sub> = 3.8 V, C<sub>VLDO</sub> = 10  $\mu$ F, L1 = 4.7  $\mu$ H, C<sub>IN</sub> = 2.2  $\mu$ F, C<sub>OUT</sub> = 4.7  $\mu$ F,  $f_{SW}$  = 1.25 MHz.



TEXAS INSTRUMENTS

## 8 Detailed Description

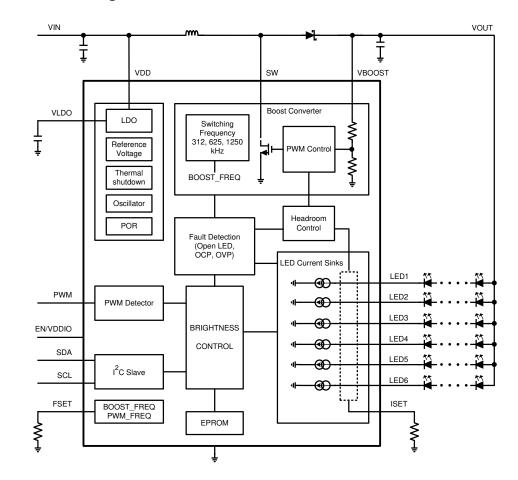
## 8.1 Overview

LP8556 is a white LED driver featuring an asynchronous boost converter and six high-precision current sinks that can be controlled by a PWM signal or an I<sup>2</sup>C master.

The boost converter uses adaptive output voltage control for setting the optimal LED driver voltages as high as 43 V. This feature minimizes the power consumption by adjusting the voltage to the lowest sufficient level under all conditions. The converter can operate at three switching frequencies: 312, 625, and 1250 kHz pre-configured via EPROM or can be set through an external resistor. Programmable slew rate control and spread spectrum scheme minimize switching noise and improve EMI performance.

LED current sinks can be set with the PWM dimming resolution of up to 15 bits. Proprietary adaptive dimming mode allows higher system power saving. In addition, phase shifted LED PWM dimming allows reduced audible noise and smaller boost output capacitors.

The LP8556 device has a full set of safety features that ensure robust operation of the device and external components. The set consists of input undervoltage lockout, thermal shutdown, overcurrent protection, up to six levels of overvoltage protection, LED open, and short detection.



#### 8.2 Functional Block Diagram



#### 8.3 Feature Description

#### 8.3.1 Boost Converter

#### 8.3.1.1 Boost Converter Operation

The LP8556 boost DC-DC converter generates a 7-V to approximately 43-V of boost output voltage from a 2.7-V to 36-V boost input voltage. The boost output voltage minimum, maximum value and range can be set digitally by pre-configuring EPROM memory (VBOOST\_RANGE, VBOOST, and VBOOST\_MAX fields).

The converter is a magnetic switching PWM mode DC-DC boost converter with a current limit. It uses CPM (current programmed mode) control, where the inductor current is measured and controlled with the feedback. During start-up, the soft-start function reduces the peak inductor current. The LP8556 has an internal 20-MHz oscillator which is used for clocking the boost. Figure 4 shows the boost block diagram.

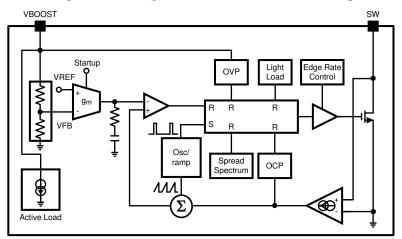


Figure 4. LP8556 Boost Converter Block Diagram

#### 8.3.1.2 Setting Boost Switching Frequency

The LP8556 boost converter switching frequency can be set either by an external resistor (BOOST\_FSET\_EN = 1 selection),  $R_{FSET}$ , or by pre-configuring EPROM memory with the choice of boost frequency (BOOST\_FREQ field). Table 1 summarizes setting of the switching frequency. Note that the  $R_{FSET}$  is shared for setting the PWM dimming frequency in addition to setting the boost switching frequency. Setting the boost switching frequency and PWM dimming frequency using an external resistor is separately shown in Table 5.

	_		
R <sub>FSET</sub> [Ω]	BOOST_FSET_EN	BOOST_FREQ[1:0]	f <sub>SW</sub> [kHz]
don't care	0	00	312
don't care	0	01	625
don't care	0	10	1250
don't care	0	11	undefined
See <sup>(1)</sup>	1	don't care	See <sup>(1)</sup>

Table 1. Configuring Boost Switching Frequency via EPRON	Table 1. Configuring	Boost	Switching	Frequency	via EPRON
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(1) See Table 5.



#### 8.3.1.3 Output Voltage Control

The LP8556 device supports two modes of controlling the boost output voltage: Adaptive Boost Voltage Control (see *Adaptive Control*) and Manual Boost Output Control (see *Manual Control*).

#### 8.3.1.3.1 Adaptive Control

LP8556 supports a mode of output voltage control called Adaptive Boost Control mode. In this mode, the voltage at the LED pins is periodically monitored by the control loop and adaptively adjusted to the optimum value based on the comparator thresholds set using LED DRIVER\_HEADROOM, LED\_COMP\_HYST, BOOST\_STEP\_UP, BOOST\_STEP\_DOWN fields in the EPROM. Settings under LED DRIVER\_HEADROOM along with LED\_COMP\_HYST fields determine optimum boost voltage for a given condition. Boost voltage is raised if the voltage measured at any of the LED strings falls below the threshold setting determined with LED DRIVER\_HEADROOM field. Likewise, boost voltage is lowered if the voltage measured at any of the LED strings is above the combined setting determined under LED DRIVER\_HEADROOM and LED\_COMP\_HYST fields. LED\_COMP\_HYST field serves to fine tune the headroom voltage for a given peak LED current. The boost voltage up/down step size can be controlled with the BOOST\_STEP\_UP and BOOST\_STEP\_DN fields.

The initial boost voltage is configured with the VBOOST field. This field also sets the minimum boost voltage. The VBOOST\_MAX field sets the maximum boost voltage. When an LED pin is open, the monitored voltage never has enough headroom, and the adaptive mode control loop keeps raising the boost voltage. The VBOOST\_MAX field allows the boost voltage to be limited to stay under the voltage rating of the external components.

#### NOTE

Only LED strings that are enabled are monitored and PS\_MODE field determines which LED strings are enabled.

The adaptive mode is selected using ADAPTIVE bit set to 1 (CFGA EPROM Register) and is the recommended mode of boost control.

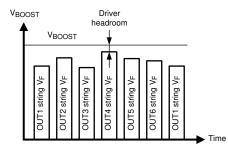


Figure 5. Boost Adaptive Control Principle

#### 8.3.1.3.2 Manual Control

User can control the boost output voltage with the VBOOST EPROM field when adaptive mode is not used. Equation 1 shows the relationship between the boost output voltage and the VBOOST field.

 $V_{BOOST} = V_{BOOST_{MIN}} + 0.42 \times VBOOST[dec]$ 

(1)

The expression is only valid when the calculated values are between the minimum boost output voltage and the maximum boost output voltage. The minimum boost output voltage is set with the VBOOST\_RANGE field. The maximum boost output voltage is set with the VBOOST\_MAX EPROM field.



#### 8.3.1.4 EMI Reduction

LP8556

The LP8556 device features two EMI reduction schemes.

The first scheme, Programmable Slew Rate Control, uses a combination of three drivers for boost switch. Enabling all three drivers allows boost switch on/off transition times to be the shortest. On the other hand, enabling just one driver allows boost switch on/off transition times to be the longest. The longer the transition times, the lower the switching noise on the SW pin. Note that the shortest transition times bring the best efficiency as the switching losses are the lowest.

EN\_DRV2 and EN\_DRV3 bits in the EPROM determine the boost switch driver configuration. Refer to the SW pin slew rate parameter listed under *Electrical Characteristics — Boost Converter* for the slew rate options.

The second EMI reduction scheme is the spread spectrum. This scheme deliberately spreads the frequency content of the boost switching waveform, which inherently has a narrow bandwidth, makes the bandwidth of the switching waveform wider, and ultimately reduces its EMI spectral density.

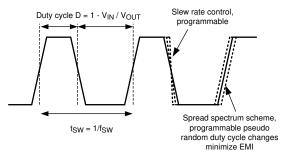


Figure 6. Principles of EMI Reduction Scheme

#### 8.3.2 Brightness Control

LP8556 enables various methods of brightness control. The brightness can be controlled using an external PWM signal or the Brightness register accessible by users via an  $I^2C$  interface or both. How these two input sources are selected and combined is set by the BRT\_MODE EPROM bits and described in *BRT\_MODE* = 00 through *BRT\_MODE* = 11, Figure 7, and Table 2. The LP8556 can also be preconfigured via EPROM memory to allow direct and unaltered brightness control by an external PWM signal. This mode of operation is obtained by setting PWM\_DIRECT EPROM bit to 1 (CFG5[7] = 1).

## 8.3.2.1 BRT\_MODE = 00

With BRT\_MODE = 00, the LED output is controlled by the PWM input duty cycle. The PWM detector block measures the duty cycle at the PWM pin and uses this 16-bit value to generate an internal to the device PWM data. Before the output is generated, the PWM data goes through the PWM curve-shaper block. Then, the data goes into the adaptive dimming function which determines the range of the PWM and Current control as described in *Output Dimming Schemes*. The outcome of the adaptive dimming function is 12-bit current and/or up to 6 PWM output signals. The current is then passed through the non-linear compensation block while the output PWM signals are channeled through the dither block.

## 8.3.2.2 BRT\_MODE = 01

With BRT\_MODE = 01, the PWM output is controlled by the PWM input duty cycle and the Brightness register. The PWM detector block measures the duty cycle at the PWM pin and uses this 16-bit value to generate the PWM data. Before the output is generated, the PWM data is first multiplied with BRT[7:0] register, then it goes through the PWM Curve Shaper block. Then, the data goes into the Adaptive Dimming function which determines the range of the PWM and Current control as described in *Output Dimming Schemes*. The outcome of the Adaptive Dimming function is 12-bit current and/or up to 6 PWM output signals. The current is then passed through the non-linear compensation block while the output PWM signals are channeled through the Dither block.



#### 8.3.2.3 BRT\_MODE = 10

With BRT\_MODE = 10, the PWM output is controlled only by the Brightness register. From BRT[7:0] register, the data goes through the PWM Curve Shaper block. Then, the data goes into the Adaptive Dimming function which determines the range of the PWM and Current control as described in *Output Dimming Schemes*. The outcome of the Adaptive Dimming function is 12-bit Current and / or up to 6 PWM output signals. The current is then passed through the non-linear compensation block while the output PWM signals are channeled through the Dither block.

#### 8.3.2.4 BRT\_MODE = 11

With BRT\_MODE = 11, the PWM control signal path is similar to the path when BRT\_MODE = 01 except that the PWM input signal is multiplied with BRT[7:0] data after the Curve-Shaper block.

PWM_DIRECT	BRT_MODE [1:0]	BRIGHTNESS CONTROL SOURCE	OUTPUT ILED FORM
0	00	External PWM signal	
0	01	External PWM signal and Brightness Register (multiplied before Curve Shaper)	Adaptive. See Output
0	10	Brightness Register	Dimming Schemes
0	11	External PWM signal and Brightness Register (multiplied after Curve Shaper)	
1	don't care	External PWM signal	Same as the external PWM input

#### Table 2. Brightness Control Methods Truth Table



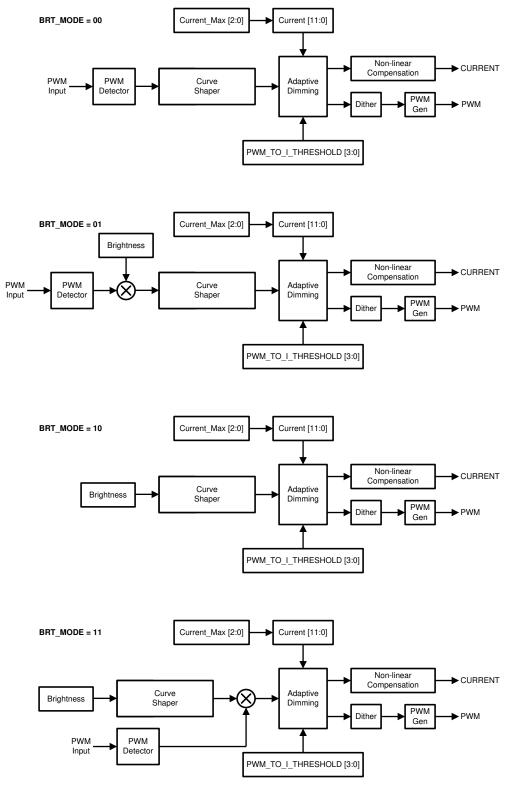


Figure 7. Brightness Control Signal Path Block Diagrams



#### 8.3.2.5 Output Dimming Schemes

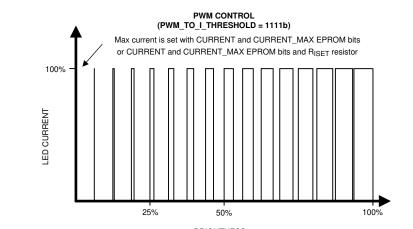
The LP8556 device supports three types of output dimming control methods: PWM Control, Pure Current Control and Adaptive Dimming (Hybrid PWM and Current) Control.

#### 8.3.2.5.1 PWM Control

PWM control is the traditional way of controlling the brightness using PWM of the outputs with the same LED current across the entire brightness range. Brightness control is achieved by varying the duty cycle proportional to the input PWM. PWM frequency is set either using an external set fesistor (R<sub>FSET</sub>) or using the PWM\_FREQ EPROM field. The maximum LED current is set by using an external set Resistor (R<sub>ISET</sub>), CURRENT, and CURRENT\_MAX EPROM bits. PWM frequency can also be set by simply using the CURRENT and CURRENT\_MAX EPROM bits.

#### NOTE

The output PWM signal is de-coupled and generated independent of the input PWM signal eliminating display flicker issues and allowing better noise immunity.

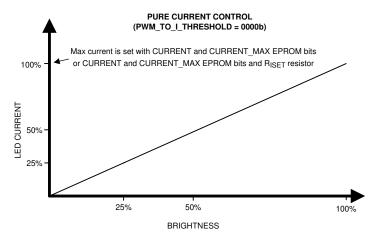


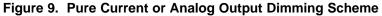
BRIGHTNESS

Figure 8. PWM Only Output Dimming Scheme

#### 8.3.2.5.2 Pure Current Control

In Pure Current Control mode, brightness control is achieved by changing the LED current proportionately from maximum value to a minimum value across the entire brightness range. Like in PWM Control mode, the maximum LED current is set by using an external set Resistor (R<sub>ISET</sub>), CURRENT, and CURRENT\_MAX EPROM bits. The maximum LED current can also be set by just using the CURRENT and CURRENT\_MAX EPROM bits. Current resolution in this mode is 12 bits.







#### 8.3.2.5.3 Adaptive Control

Adaptive dimming control combines PWM Control and Pure Current Control dimming methods. With the adaptive dimming, it is possible to achieve better optical efficiency from the LEDs compared to pure PWM control while still achieving smooth and accurate control at low brightness levels. Current resolution in this mode is 12 bits. Switch point from Current to PWM control can be set with the PWM\_TO\_I\_THRESHOLD EPROM field from 0% to 100% of the brightness range to get good compromise between good matching of the LEDs brightness/white point at low brightness and good optical efficiency.

PWM frequency is set either using an external set Resistor (R<sub>FSET</sub>) or using the PWM\_FREQ EPROM bits. The maximum LED current is set either by using an external set Resistor (R<sub>ISET</sub>), CURRENT, and CURRENT\_MAX EPROM bits. Or the maximum LED current may be set using the CURRENT and CURRENT\_MAX EPROM bits.

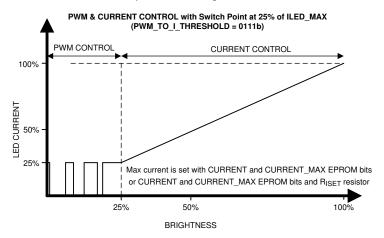


Figure 10. Adaptive Output Dimming Scheme

#### 8.3.2.6 Setting Full-Scale LED Current

The maximum or full-scale LED current is set either using an external set Resistor ( $R_{ISET}$ ), CURRENT, and CURRENT\_MAX EPROM bits or just by using the CURRENT and CURRENT\_MAX EPROM bits. Table 3 summarizes setting of the full-scale LED current.

R <sub>ISET</sub> [Ω]	ISET_EN	CURRENT_MAX	CURRENT[11:0]	FULL-SCALE ILED [mA]
don't care	0	000	FFFh	5
don't care	0	001	FFFh	10
don't care	0	010	FFFh	15
don't care	0	011	FFFh	20
don't care	0	100	FFFh	23
don't care	0	101	FFFh	25
don't care	0	110	FFFh	30
don't care	0	111	FFFh	50
don't care	0	000 - 111	001h - FFFh	See <sup>(1)</sup>
24k	1	000	FFFh	5
24k	1	001	FFFh	10
24k	1	010	FFFh	15
24k	1	011	FFFh	20
24k	1	100	FFFh	23
24k	1	101	FFFh	25
24k	1	110	FFFh	30
24k	1	111	FFFh	50
12k - 100k	1	000 - 111	001h - FFFh	See <sup>(1)</sup>

Table 3. Setting Full-Scale LED Current

(1) See CFG0.



## 8.3.2.7 Setting PWM Dimming Frequency

LP8556 PWM dimming frequency can be set by an external resistor,  $R_{FSET}$ , or by pre-configuring EPROM Memory (CFG5 register, PWM\_FREQ[3:0] bits). Table 4 summarizes setting of the PWM dimming frequency. Note that .

#### NOTE

The  $R_{FSET}$  is shared for setting the boost switching frequency, too. Setting the boost switching frequency and PWM dimming frequency using an external resistor is shown in Table 5.

R <sub>FSET</sub> [kΩ]	PWM_FSET_EN	PWM_FREQ[3:0]	f <sub>PWM</sub> [Hz] (Resolution)		
		0000	4808 (11-bit)		
		0001	6010 (10-bit)		
		0010	7212 (10-bit)		
		0011	8414 (10-bit)		
		0100	9616 (10-bit)		
		0101	12020 (9-bit)		
		0110	13222 (9-bit)		
don't care	0	0111	14424 (9-bit)		
dont care		0	1000	15626 (9-bit)	
					1001
		1010	18030 (9-bit)		
		1011	19232 ((9-bit)		
		1100	24040 (8-bit)		
		1101	28848 (8-bit)		
		1110	33656 (8-bit)		
		1111	38464 (8-bit)		
See <sup>(1)</sup>	1	don't care	See <sup>(1)</sup>		

#### Table 4. Configuring PWM Dimming Frequency via EPROM

(1) See Table 5.



# Table 5. Setting Switching and PWM Dimming Frequency With an External Resistor

R <sub>FSET</sub> [Ω] (Tolerance)	f <sub>sw</sub> [kHz]	f <sub>PWM</sub> [Hz] (Resolution)
Floating or FSET pin pulled HIGH	1250	9616 (10-bit)
470k - 1M (±5%)	312	2402 (12-bit)
300k, 330k (±5%)	312	4808 (11-bit)
200k (±5%)	312	6010 (10-bit)
147k, 150k, 154k, 158k (±1%)	312	9616 (10-bit)
121k (±1%)	312	12020 (9-bit)
100k (±1%)	312	14424 (9-bit)
86.6k (±1%)	312	16828 (9-bit)
75.0k (±1%)	312	19232 (9-bit)
63.4k (±1%)	625	2402 (12-bit)
52.3k, 53.6k (±1%)	625	4808 (11-bit)
44.2k, 45.3k (±1%)	625	6010 (10-bit)
39.2k (±1%)	625	9616 (10-bit)
34.0k (±1%)	625	12020 (9-bit)
30.1k (±1%)	625	14424 (9-bit)
26.1k (±1%)	625	16828 (9-bit)
23.2k (±1%)	625	19232 (9-bit)
20.5k (±1%)	1250	2402 (12-bit)
18.7k (±1%)	1250	4808 (11-bit)
16.5k (±1%)	1250	6010 (10-bit)
14.7k (±1%)	1250	9616 (10-bit)
13.0k (±1%)	1250	12020 (9-bit)
11.8k (±1%)	1250	14424 (9-bit)
10.7k (±1%)	1250	16828 (9-bit)
9.76k (±1%)	1250	19232 (9-bit)
FSET pin shorted to GND	1250	Same as PWM input

#### 8.3.2.8 Phase Shift PWM Scheme

Phase shift PWM scheme allows delaying the time when each LED driver is active. When the LED drivers are not activated simultaneously, the peak load current from the boost output is greatly decreased. This reduces the ripple seen on the boost output and allows smaller output capacitors. Reduced ripple also reduces the output ceramic capacitor audible ringing. PSPWM scheme also increases the load frequency seen on the boost output six times and therefore transfers the possible audible noise to the frequencies outside of the audible range.

Description of the PSPWM mode is seen inTable 6. PSPWM mode is set with <PS\_MODE[2:0]> bits.

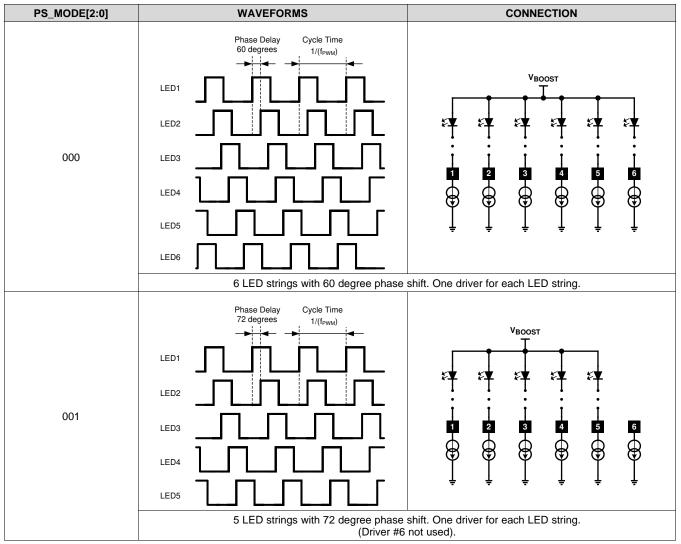


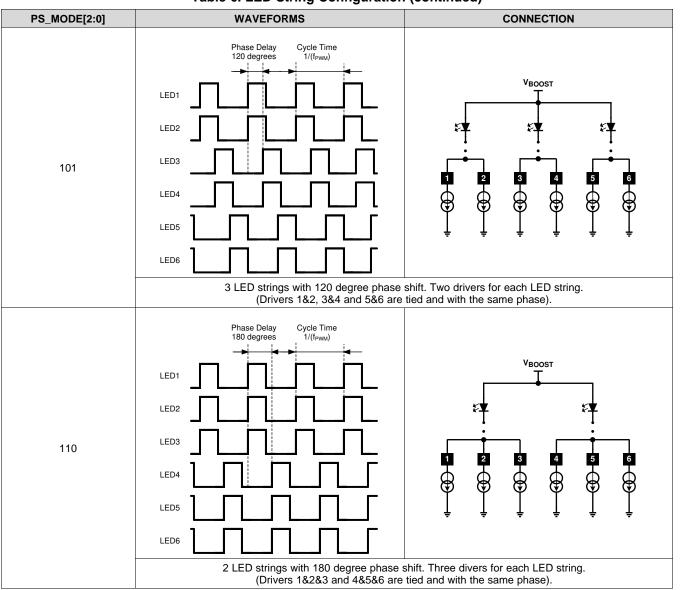
 Table 6. LED String Configuration



WAVEFORMS PS\_MODE[2:0] CONNECTION Cycle Time 1/(f<sub>PWM</sub>) Phase Delay VBOOST 90 degrees LED1 LED2 010 2 5 3 4 LED3 Ê Ê Ê LED4 4 LED strings with 90 degree phase shift. One driver for each LED string. (Drivers #5 and #6 not used). VBOOST Phase Delay Cycle Time 120 degrees 1/(f<sub>PWM</sub>) 1 LED1 011 LED2 2 4 5 Ê Ê LED3 3 LED strings with 120 degree phase shift. One driver for each LED string. (Drivers #4, #5 and #6 not used). VBOOST Cycle Time 1/(f<sub>PWM</sub>) Phase Delay 180 degrees LED1 100 2 LED2 Ĵ 2 LED strings with 180 degree phase shift. One driver for each LED string. (Drivers #3, #4, #5 and #6 not used).

#### Table 6. LED String Configuration (continued)

LP8556 JAJSEF5L – JULY 2012–REVISED MAY 2019



## Table 6. LED String Configuration (continued)



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	Table 6. LED String Configuration	ו (continued)
PS_MODE[2:0]	WAVEFORMS	CONNECTION
111	Phase Delay Cycle Time 0 degrees 1/(f <sub>PWM</sub> ) LED1 LED2 LED3 LED4 LED5 LED6 LED6	

1 LED string driven by all six drivers. (All drivers are tied and with the same phase).

#### .. - -. . --. ---\_ . . \_ . . \_ . .



#### 8.3.2.9 Slope and Advanced Slope

Transition time between two brightness values can be programmed with EPROM bits <PWM\_SLOPE[2:0]> from 0 to 500 ms. Same slope time is used for sloping up and down. With advanced slope the brightness changes can be made more pleasing to a human eye.

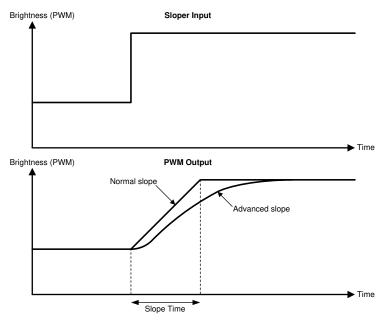


Figure 11. Sloper Operation

#### 8.3.2.10 Dithering

Special dithering scheme can be used during brightness changes and in steady state condition. It allows increased resolution and smaller average steps size during brightness changes. Dithering can be programmed with EPROM bits <DITHER[1:0]> from 0 to 3 bits. <STEADY\_DITHER> EPROM bit sets whether the dithering is used also in steady state or only during slopes. Example below is for 1-bit dithering. For 3-bit dithering, every 8th pulse is made 1 LSB longer to increase the average value by 1/8th.

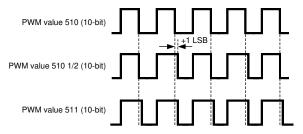


Figure 12. Example of the Dithering, 1-bit Dither, 10-bit Resolution



#### 8.3.3 Fault Detection

LP8556 has fault detection for LED open and short conditions, UVLO, overcurrent, and thermal shutdown. The cause for the fault can be read from status register. Reading the fault register also resets the fault.

#### 8.3.3.1 LED Fault Detection

With LED fault detection, the voltages across the LED drivers are constantly monitored. Shorted or open LED strings are detected.

#### 8.3.3.1.1 Open Detect

The logic uses the LOW comparators and the requested boost voltage to detect the OPEN condition. If the logic is asking the boost for the maximum allowed voltage and a LOW comparator is asserted, then the OPEN bit is set in the STATUS register (ADDR = 02h). In normal operation, the adaptive headroom control loop raises the requested boost voltage when the LOW comparator is asserted. If it has raised it as high as it can and an LED string still needs more voltage, then it is assumed to be disconnected from the boost voltage (open or grounded). The actual boost voltage is not part of the OPEN condition decision; only the requested boost voltage and the LOW comparators.

#### 8.3.3.1.2 Short Detect

The logic uses all three comparators (HIGH, MID and LOW) to detect the SHORT condition. When the MID and LOW comparators are de-asserted, the headroom control loop considers that string to be optimized - enough headroom, but not excessive. If at least one LED string is optimized and at least one other LED string has its HIGH comparator asserted, then the SHORT condition is detected. It is important to note that the SHORT condition requires at least two strings for detection: one in the optimized headroom zone (LOW/MID/HIGH comparators all de-asserted) and one in the excessive headroom zone (HIGH comparator asserted).

Fault is cleared by reading the fault register.

#### 8.3.3.2 Undervoltage Detection

The LP8556 device has detection for too-low  $V_{IN}$  voltage. Threshold level for the voltage is set with EPROM register bits as shown in Table 7.

UVLO_EN	UVLO_TH	THRESHOLD (V)
0	don't care	OFF
1	0	2.5
1	1	5.2

When undervoltage is detected the LED outputs and the boost shuts down, and the corresponding fault bit is set in the fault register. The LEDs and the boost start again when the voltage has increased above the threshold level. Hysteresis is implemented to threshold level to avoid continuous triggering of fault when threshold is reached.

Fault is cleared by setting the EN / VDDIO pin low or by reading the fault register.

#### 8.3.3.3 Overcurrent Protection

LP8556 has detection for too-high loading on the boost converter. When overcurrent fault is detected, the boost shuts down and the corresponding fault bit is set in the fault register. The boost starts again when the current has dropped below the OCP threshold.

Fault is cleared by reading the fault register.

#### 8.3.3.4 Thermal Shutdown

If the LP8556 reaches thermal shutdown temperature (150°C) the LED outputs and boost shut down to protect it from damage. The device re-activates when temperature drops below 130°C.

Fault is cleared by reading the fault register.



## 8.4 Device Functional Modes

#### 8.4.1 Shutdown Mode

The device is in shutdown mode when the EN/VDDIO input is low. Current consumption in this mode from VDD pin is < 1.6  $\mu$ A.

#### 8.4.2 Active Mode

In active mode the backlight is enabled either with setting the ON register bit high (BRTMODE = 0 1, 10, 11) or by activating PWM input (BRTMODE=00). The powers supplying the VDD and EN/VDDIO pins must be present. Brightness is controlled with  $I^2C$  writes to brightness registers or by changing PWM input duty cycle (operation without  $I^2C$  control). Configuration registers are not accessible in Active mode to prevent damage to the device by accidental writes. Current consumption from VDD pin this mode is typically 2.2 mA when boost is enabled and LEDs are not drawing any current.

## 8.5 Programming

#### 8.5.1 I<sup>2</sup>C-Compatible Serial Bus Interface

#### 8.5.1.1 Interface Bus Overview

The I<sup>2</sup>C-compatible synchronous serial interface provides access to the programmable functions and registers on the device. This protocol uses a two-wire interface for bidirectional communications between the ICs connected to the bus. The two interface lines are the Serial Data Line (SDA) and the Serial Clock Line (SCL). These lines must be connected to a positive supply via a pull-up resistor and remain HIGH even when the bus is idle.

Every device on the bus is assigned a unique address and acts as either a Master or a Slave depending on whether it generates or receives the SCL. The LP8556 can operate as an  $I^2C$  slave.

#### 8.5.1.2 Data Transactions

One data bit is transferred during each clock pulse. Data is sampled during the high state of the serial clock SCL. Consequently, throughout the clock's high period, the data should remain stable. Any changes on the SDA line during the high state of the SCL and in the middle of a transaction, aborts the current transaction. New data should be sent during the low SCL state. This protocol permits a single data line to transfer both command/control information and data using the synchronous serial clock.

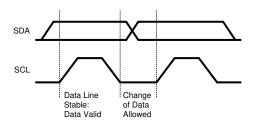


Figure 13. Bit Transfer

Each data transaction is composed of a Start Condition, a number of byte transfers (set by the software) and a Stop Condition to terminate the transaction. Every byte written to the SDA bus must be 8 bits long and is transferred with the most significant bit first. After each byte, an Acknowledge signal must follow. The following sections provide further details of this process.



## **Programming (continued)**

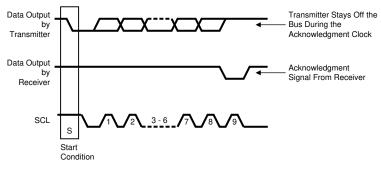


Figure 14. Start and Stop

The Master device on the bus always generates the Start and Stop Conditions (control codes). After a Start Condition is generated, the bus is considered busy and it retains this status until a certain time after a Stop Condition is generated. A high-to-low transition of the data line (SDA) while the clock (SCL) is high indicates a Start Condition. A low-to-high transition of the SDA line while the SCL is high indicates a Stop Condition.

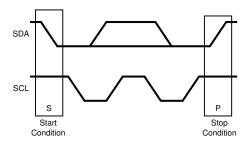


Figure 15. Start and Stop Conditions

In addition to the first Start Condition, a repeated Start Condition can be generated in the middle of a transaction. This allows another device to be accessed, or a register read cycle.

#### 8.5.1.3 Acknowledge Cycle

The Acknowledge Cycle consists of two signals: the acknowledge clock pulse the master sends with each byte transferred, and the acknowledge signal sent by the receiving device.

The master generates the acknowledge clock pulse on the ninth clock pulse of the byte transfer. The transmitter releases the SDA line (permits it to go high) to allow the receiver to send the acknowledge signal. The receiver must pull down the SDA line during the acknowledge clock pulse and ensure that SDA remains low during the high period of the clock pulse, thus signaling the correct reception of the last data byte and its readiness to receive the next byte.

#### 8.5.1.4 Acknowledge After Every Byte Rule

The master generates an acknowledge clock pulse after each byte transfer. The receiver sends an acknowledge signal after every byte received.

There is one exception to the *acknowledge after every byte* rule. When the master is the receiver, it must indicate to the transmitter an end of data by not-acknowledging ("negative acknowledge") the last byte clocked out of the slave. This *negative acknowledge* still includes the acknowledge clock pulse (generated by the master), but the SDA line is not pulled down.



#### **Programming (continued)**

#### 8.5.1.5 Addressing Transfer Formats

Each device on the bus has a unique slave address. The LP8556 operates as a slave device with 7-bit address combined with data direction bit. Slave address is 2Ch as 7-bit or 58h for write and 59h for read in 8-bit format.

Before any data is transmitted, the master transmits the slave I.D. The slave device should send an acknowledge signal on the SDA line, once it recognizes its address.

The slave address is the first seven bits after a Start Condition. The direction of the data transfer (R/W) depends on the bit sent after the slave address — the 8th bit.

When the slave address is sent, each device in the system compares this slave address with its own. If there is a match, the device considers itself addressed and sends an acknowledge signal. Depending upon the state of the R/W bit (1:read, 0:write), the device acts as a transmitter or a receiver.

MSB			_				LSB	_
ADR6 Bit7	ADR5 bit6	ADR4 bit5	ADR3 bit4	ADR2 bit3	ADR1 bit2	ADR0 bit1	R/W bit0	
х	x	х	х	х	х	х		
•	— I <sup>2</sup> C	SLAVE a	address (	chip add	ress) —			

Figure 16. I<sup>2</sup>C Chip Address (0x2C)

#### 8.5.1.6 Control Register Write Cycle

- Master device generates start condition.
- Master device sends slave address (7 bits) and the data direction bit (r/w = 0).
- Slave device sends acknowledge signal if the slave address is correct.
- Master sends control register address (8 bits).
- Slave sends acknowledge signal.
- Master sends data byte to be written to the addressed register.
- Slave sends acknowledge signal.
- If master sends further data bytes the control register address is incremented by one after acknowledge signal.
- Write cycle ends when the master creates stop condition.

#### 8.5.1.7 Control Register Read Cycle

- Master device generates a start condition.
- Master device sends slave address (7 bits) and the data direction bit (r/w = 0).
- Slave device sends acknowledge signal if the slave address is correct.
- Master sends control register address (8 bits).
- Slave sends acknowledge signal.
- Master device generates repeated start condition.
- Master sends the slave address (7 bits) and the data direction bit (r/w = 1).
- · Slave sends acknowledge signal if the slave address is correct.
- Slave sends data byte from addressed register.
- If the master device sends acknowledge signal, the control register address is incremented by one. Slave device sends data byte from addressed register.
- Read cycle ends when the master does not generate acknowledge signal after data byte and generates stop condition.



## **Programming (continued)**

#### Table 8. Data Read and Write Cycles

	ADDRESS MODE
Data Read	<start condition=""> <slave address=""><r w="0">[Ack] <register addr.="">[Ack] <repeated condition="" start=""> <slave address=""><r w="1">[Ack] [Register Data]<ack nack="" or="">  additional reads from subsequent register address possible <stop condition=""></stop></ack></r></slave></repeated></register></r></slave></start>
Data Write	<start condition=""> <slave address=""><r w="0">[Ack] <register addr.="">[Ack] <register data="">[Ack]  additional writes to subsequent register address possible <stop condition=""></stop></register></register></r></slave></start>

<>Data from master [] Data from slave

#### 8.5.1.8 Register Read and Write Detail

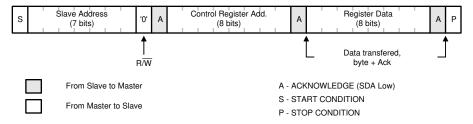


Figure 17. Register Write Format

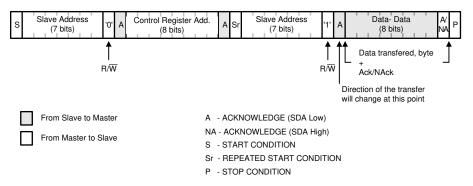


Figure 18. Register Read Format

# 8.6 Register Maps

# Table 9. Register Map

ADDR	REGISTER	D7	D6	D5	D4	D3	D2	D1	D0	RESET
00H	Brightness Control				BRT[7:0]					
01H	Device Control	FAST					BRT_	BRT_MODE		0000 0000
02H	Status	OPEN	SHORT	VREF_OK	VBOOST_OK	OVP	OCP	TSD	UVLO	0000 0000
04H	Direct Control				LED					
16H	LED Enable					LEI	D_EN			0011 1111

## Table 10. EPROM Memory Map

ADDR	REGISTER	D7	D6	D5	D4	D3	D2	D1	D0	
98H	CFG98	IBOOST_LIM_2X		RESERVED RESERVED						
9EH	CFG9E	RESERV	ED	VBOOST_RANGE	RESERVED		HEADR	DOM_OFFSET		
A0H	CFG0				С	URRENT LSB				
A1H	CFG1	PDET_STDBY		CURRENT_MAX			CUR	RENT MSB		
A2H	CFG2	RESERV	ED	UVLO_EN	UVLO_TH	BL_ON	ISET_EN	BOOST_FSET_EN	PWM_FSET_EN	
A3H	CFG3	RESERVED		SLOPE		FI	LTER	PWM_INPUT_	HYSTERESIS	
A4H	CFG4	PWM_TO_		I_THRESHOLD		RESERVED STEADY_DITHE DITHER R DITHER			IER	
A5H	CFG5	PWM_DIRECT		PS_MODE		PWM_FREQ				
A6H	CFG6	BOOST_FF	REQ	EQ			VBOOST			
A7H	CFG7	RESERV	ED	EN_DRV3	EN_DRV2	RES	ERVED	IBOOS	IBOOST_LIM	
A8H	CFG8	RESERV	ED	RESERV	ED	RES	ERVED	RESE	RVED	
A9H	CFG9		VBOOST_M	λX	JUMP_EN	JUMP_TI	HRESHOLD	JUMP_V	OLTAGE	
AAH	CFGA	SSCLK_EN	RESERVE D	RESERV	ED	ADAPTIVE		DRIVER_HEADROOM	Л	
ABH	CFGB					RESERVED				
ACH	CFGC		RES	SERVED			RE	SERVED		
ADH	CFGD					RESERVED				
AEH	CFGE	STEP_U	P	STEP_D	N	LED_FAULT_TH LED_COMP_HYST			/P_HYST	
AFH	CFGF					REVISION				



## 8.6.1 Register Bit Explanations

## 8.6.1.1 Brightness Control

Address 00h

#### Reset value 0000 0000b

BRIGHTNESS	BRIGHTNESS CONTROL REGISTER												
7	6	5	4 3 2 1 0										
	BRT[7:0]												
NAME	NAME BIT ACCESS DESCRIPTION												
BRT	BRT 7:0 R/W Backlight PWM 8-bit linear control.												

#### 8.6.1.2 Device Control

#### Address 01h

Reset value 0000 0000b

## DEVICE CONTROL REGISTER

DEVICE CONTR	COL REGISTE	=R									
7	6	5	4	3	2	1	0				
FAST			BRT_MODE[1:0] BL_CTL								
NAME	BIT	ACCESS	DESCRIPTIC	DN							
FAST	7		power STAN 0 = read EPF		turning to the	ACTIVE state	s when exiting the low				
BRT_MODE	2:1	R/W	Brightness so	ource mode Fig	ure 7						
			00b = PWM i	nput only							
			01b = PWM i	nput and Bright	ness register	(combined before	shaper block)				
			10b = Brightr	ness register on	ly						
			11b = PWM i	nput and Bright	ness register	(combined after sh	aper block)				
BL_CTL	0	R/W	Enable backl (BRT_MODE		tness Registe	r is used to contro	l brightness				
			0 = Backlight disabled and chip turned off 1 = Backlight enabled and chip turned on								
			This bit has no effect when PWM pin control is selected for brightness control (BRT_MODE = 00). In this mode the state of PWM pin enable or disables the chip.								

TEXAS INSTRUMENTS

## 8.6.1.3 Status

Address 02h

Reset value 0000 0000b

FAULT REGIST	ER											
7	6	5	4	3	2	1	0					
OPEN	SHORT	VREF_OK	VBOOST_OK	OVP	OCP	TSD	UVLO					
NAME	BIT	ACCESS	DESCRIPTION									
OPEN	7	R	LED open fault detection									
			0 = No fault									
			1 = LED open fault de	1 = LED open fault detected. The value is not latched.								
SHORT	6	R	LED short fault detect	tion								
			0 = No fault									
			1 = LED short fault de	etected. The value is	s not latched.							
VREF_OK	5	R	Internal VREF node n	nonitor status								
			1 = VREF voltage is 0	OK.								
VBOOST_OK	4	R	Boost output voltage	monitor status								
			0 = Boost output volta	age has not reached	l its target (VBO	OST < Vtarget -	– 2.5V)					
			1 = Boost output volta	age is OK. The value	e is not latched.							
OVP	3	R	Overvoltage protection									
			0 = No fault									
			1 = Overvoltage cond	ition occurred. Fault	t is cleared by re	eading the regis	ter 02h.					
OCP	2	R	Over current protection									
			0 = No fault									
			1 = Overcurrent cond	ition occurred. Fault	bit is cleared by	y reading this re	gister.					
TSD	1	R	Thermal shutdown									
			0 = No fault									
		1 = Thermal fault generated, 150°C reached. Boost converter and LED outputs are disabled until the temperature has dropped down to 130°C. Fault is cleared by readi this register.										
UVLO	0	R	Undervoltage detection	n								
			0 = No fault									
			1 = Undervoltage detected on the $V_{DD}$ pin. Boost converter and LED outputs are disabled until $V_{DD}$ voltage is above the UVLO threshold voltage. Threshold voltage is set with EPROM bits. Fault is cleared by reading this register.									

## 8.6.1.4 Direct Control

Address 04h

Reset value 0000 0000b

DIRECT CONTROL REGISTER													
7	6	5	4	3	2	1	0						
				OUT	[5:0]								
NAME	BIT	ACCESS	DESCRIPTION										
OUT	5:0	R/W	Direct control of t	he LED outputs									
			0 = Normal opera	ation. LED output	are controlled with	n the adaptive	dimming block						
			1 = LED output is	s forced to 100%	PWM.								

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## 8.6.1.5 LED String Enable

Address 16h

## Reset value 0011 1111b

## TEMP LSB REGISTER

TEMP LSB REGISTER							
7	6	5	4	3	2	1	0
		LED_EN[5:0]					
NAME	BIT	ACCESS DESCRIPTION					
LED_EN	5:0	R/W	R/W Bits 5:0 correspond to LED Strings 6:1 respectively. Bit value 1 = LED String Enabled Bit value 0 = LED String Disabled Note: To disable string(s), it is recommended to disable higher order string(s). For example, for 5-string configuration, disable 6th String. For 4-string configuration, disable 6th and 5th string. These bits are ANDed with the internal LED enable bits that are generated with the PS_MODE logic.				

## 8.6.2 EPROM Bit Explanations

8.6.2.1	LP8556TM (DSBGA)	Configurations and	I Pre-Configured EPROM Settings	5
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ADDRESS	LP8556-E02	LP8556-E03	LP8556-E04	LP8556-E05 <sup>(1)</sup>
98h[7]	Ob	0b	Ob	0b
9Eh	22h	24h	24h	22h
A0h	FFh	FFh	FFh	
A1h	5Fh	BFh	3Fh	
A2h	20h	28h	2Fh	
A3h	5Eh	5Eh	5Eh	
A4h	72h	72h	72h	
A5h	04h	14h	04h	
A6h	80h	80h	80h	
A7h	F7h	F7h	F7h	
A9h	80h	A0h	60h	
AAh	0Fh	0Fh	0Fh	
ABh	00h	00h	00h	
ACh	00h	00h	00h	
ADh	00h	00h	00h	
AEh	0Fh	0Fh	0Fh	
AFh	05h	03h	03h	

(1) LP8556-E05 is a device option with un-configured EPROM settings. This option is for users that desire programming the device by themselves. Bits 98h[7] and 9Eh[5] are always pre-configured.

## 8.6.2.2 LP8556TM (DSBGA) Configurations and Pre-configured EPROM Settings Continued

ADDRESS	LP8556-E06	LP8556-E07	LP8556-E09	LP8556-E11
98h[7]	Ob	Ob	Ob	0b
9Eh	22h	04h	22h	02h
A0h	FFh	FFh	FFh	FFh
A1h	DBh	BFh	CFh	4Fh
A2h	2Fh	0Dh	2Fh	20h
A3h	02h	02h	02h	03h
A4h	72h	72h	72h	12h
A5h	14h	20h	04h	3Ch
A6h	40h	4Eh	80h	40h
A7h	F7h	F6h	F7h	F4h
A9h	DBh	C0h	A0h	80h
AAh	0Fh	0Fh	0Fh	0Fh
ABh	00h	00h	00h	00h
ACh	00h	00h	00h	00h
ADh	00h	00h	00h	00h
AEh	0Fh	0Fh	0Eh	0Fh
AFh	05h	03h	05h	01h

#### 8.6.2.3 LP8556SQ (WQFN) Configurations and Pre-configured EPROM Settings

ADDRESS	LP8556-E00	LP8556-E08	LP8556-E09
98h[7]	1b	1b	1b
9Eh	22h	22h	22h
A0h	FFh	FFh	FFh
A1h	CFh	CFh	CFh
A2h	2Fh	2Fh	2Fh
A3h	5Eh	5Eh	02h
A4h	72h	72h	72h
A5h	14h	24h	04h
A6h	80h	80h	80h
A7h	F6h	F6h	F6h
A9h	A0h	A0h	A0h
AAh	0Fh	0Fh	0Fh
ABh	00h	00h	00h
ACh	00h	00h	00h
ADh	00h	00h	00h
AEh	0Fh	0Fh	0Fh
AFh	01h	01h	01h

#### 8.6.2.4 CFG98

Address 98h

CFG98 REGISTER										
7	6	5	4	3	2	1	0			
IBOOST_LIM_2X										
NAME	BIT	ACCESS	DESCRIPTION							
IBOOST_LIM_2X	7	R/W	A. When IBOOST_LIM	_2X = 0, the ind _2X = 1, the ind	je. luctor current limit car luctor current limit car QFN package and not	be set to 1.6 A, 2	2.1 A, or 2.6 A .			

 1.8 A is the maximum I<sub>SW\_LIM</sub> supported with the DSBGA package. For applications requiring the I<sub>SW\_LIM</sub> to be greater than 1.8 A and up to 2.6 A, WQFN package should be considered.



#### LP8556 JAJSEF5L – JULY 2012–REVISED MAY 2019

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#### 8.6.2.5 CFG9E

Address 9Eh

CFG9E REGISTER										
7	6	5	4	3	2	1	0			
		VBOOST_RANGE	HEADROOM_OFFSET							
NAME	BIT	ACCESS	DESCRIPTION							
VBOOST_RANGE	5	R/W	Select VBOOST range. When VBOOST_RANGE = 0, the output voltage range is from 7 V to 34 V When VBOOST_RANGE = 1, the output voltage range is from 16 V to 43 V In applications with an output voltage higher than 16 V, VBOOST_RANGE = 1 is preferred.							
HEADROOM_ OFFSET	3:0	R/W	LED driver headroom offset. This adjusts the LOW comparator threshold together with LED_HEADROOM bits and contributes to the MID comparator threshold. 0000 = 460 mV 0001 = 390 mV 0010 = 320 mV 0100 = 250 mV 1000 = 180 mV							

### 8.6.2.6 CFG0

Address A0h

CFG0 REGISTER								
7	6	5	4	3	2	1	0	
			CURRE	NT LSB[7:0]				
NAME	BIT	ACCESS	DESCRIPTION					
CURRENT LSB	7:0	R/W	LED current to be current set using 0, the LED current	register (LSB) along the set in 12-bit fine steps CFG1 Register, CURR t is defined with the bit connected to the ISET p	. These 12-bits ENT_MAX bits ( s as shown belo	further scale the m (denoted as IMAX) w. If ISET_EN = 1	aximum LED ). If ISET_EN = , then the	
					ISET_EN = 0	ISET_E	N = 1	
			0000	0000 0000	0A	0A		
			0000	0000 0001	(1/4095) × I <sub>MAX</sub>	(1/4095) × I <sub>MAX</sub> × 20,000 × 1 / R <sub>ISET</sub>		
			0000	0000 0010	(2/4095) × I <sub>MAX</sub>	(2/4095) x I <sub>MAX</sub> × / R <sub>IS</sub>		
			0111	1111 1111	(2047/4095) × I <sub>MAX</sub>	(2047/4095) × I <sub>N</sub> 1.2V / F		
			1111	1111 1101	(4093/4095) × I <sub>MAX</sub>	(4093/4095) × I <sub>MAX</sub> × 20,000 1.2V / R <sub>ISET</sub>		
			1111	1111 1110	(4094/4095) × I <sub>MAX</sub>	(4094/4095) × I <sub>N</sub> 1.2V / F		
			1111	1111 1111	(4095/4095) × I <sub>MAX</sub>	(4095/4095) × I <sub>N</sub> 1.2V / F		



Address A1h

G1 REGISTER							
7	6	5	4	3	2	1	0
PDET_STDBY	C	URRENT_MAX	[2:0]		CURREN	T MSB[11:8]	
NAME	BIT	ACCESS	DESCRIPTION	N			
PDET_STDBY	7	R/W	Enable Standby when PWM input is constant low (approx. 50 ms timeout).				
CURRENT_MAX	6:4	R/W	Set Maximum described in th 000 = 5  mA 001 = 10  mA 010 = 15  mA 011 = 20  mA 100 = 23  mA 101 = 25  mA 111 = 50  mA		s shown below. This r ter.	naximum current i	s scaled as
CURRENT MSB	3:0	R/W	These bits forr	n the 4 MSB bi	ts for LED Current as	described in CFG	60 Register.

## 8.6.2.8 CFG2

Address A2h

CFG2 REGISTER								
7	6	5	4	3	2	1	0	
RESERVED		UVLO_EN					PWM_ _FSET_EN	
NAME	BIT	ACCESS	DESCRIPTION	N				
RESERVED	7:6	R/W						
UVLO_EN	5	R/W	Undervoltage I	ockout protectio	on enable.			
UVLO_TH	4	R/W	UVLO threshold levels: 0 = 2.5 V 1 = 5.2 V					
BL_ON	3	R/W	Enable backlight. This bit must be set for PWM only control. 0 = Backlight disabled. This selection is recommended for systems with an I <sup>2</sup> C master. With an I <sup>2</sup> C master, the backlight can be controlled by writing to the register 01h. 1 = Backlight enabled. This selection is recommended for systems with PWM only control.					
ISET_EN	2	R/W	0 = Resistor is EPROM regist 1 = Resistor is	er bits. enabled and cu	urrent is set with	the R <sub>ISET</sub> resist	d CURRENT_MAX	
BOOST_FSET_EN	1	R/W	Enable configuration of the switching frequency via FSET pin. 0 = Configuration of the switching frequency via FSET pin is is disabled. The switching frequency is set with BOOST_FREQ EPROM register bits. 1 = Configuration of the switching frequency via FSET pin is is enabled.					
PWM_FSET_EN	0	R/W	0 = Configurat switching frequ	ion of the switch Jency is set with	ning frequency v n PWM_FREQ E	quency via FSE /ia FSET pin is is EPROM register ency via FSET p	s disabled. The bits.	

TEXAS INSTRUMENTS
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LP8556 JAJSEF5L-JULY 2012-REVISED MAY 2019

## 8.6.2.9 CFG3

Address A3h

CFG3 REGISTER								
7	6	5	4	3	2	1	0	
RESERVED		SLOPE[2:0]	FILTER[1:0] PWM_INPUT_HYSTERES				HYSTERESIS[1:0]	
NAME	BIT	ACCESS	DESCRIPTION					
RESERVED	7	R/W						
SLOPE	6:4	R/W		ess change trans nmediate change				
FILTER	3:2	R/W	Select brightness change transition filtering strength 00 = No filtering 01 = light smoothing 10 = medium smoothing 11 = heavy smoothing					
PWM_INPUT_ _HYSTERESIS	1:0	R/W	00 = OFF 01 = 1-bit hyst 10 = 1-bit hyst	steresis function eresis with 13-b eresis with 12-b eresis with 8-bit	it resolution it resolution			

### 8.6.2.10 CFG4

#### Address A4h

CFG4 REGISTER	FG4 REGISTER									
7	6	5	4	3	2	1	0			
PWM_TO	_I_THRE	SHOLD[3:0]	RESERVED STEADY_ DITHER[1:0] _DITHER				HER[1:0]			
NAME	BIT	ACCESS	DESCRIPTION							
PWM_TO_I_THRESHOLD	7:4	R/W	Select switch point between PWM and pure current dimming 0000 = current dimming across entire range 0001 = switch point at <b>10%</b> of the maximum LED current. 0010 = switch point at <b>12.5%</b> of the maximum LED current. 0011 = switch point at <b>17.5%</b> of the maximum LED current. 0100 = switch point at <b>17.5%</b> of the maximum LED current. 0111 = switch point at <b>20%</b> of the maximum LED current. 0110 = switch point at <b>22.5%</b> of the maximum LED current. 0111 = switch point at <b>25%</b> of the maximum LED current. 0111 = switch point at <b>25%</b> of the maximum LED current. 1000 = switch point at <b>33.33%</b> of the maximum LED current. 1001 = switch point at <b>41.67%</b> of the maximum LED current. 1010 = switch point at <b>50%</b> of the maximum LED current. 1011 = SWITCH point at <b>50%</b> of the maximum LED current. 1011 = SWITCH point at <b>50%</b> of the maximum LED current.							
RESERVED	3	R/W								
STEADY_DITHER	2	R/W	Dither function method select: 0 = Dither only on transitions 1 = Dither at all times							
DITHER	1:0	R/W	Dither function control 00 = Dithering disabled 01 = 1-bit dithering 10 = 2-bit dithering 11 = 3-bit dithering							



## 8.6.2.11 CFG5

Address A5h

**CFG5 REGISTER** 

LP8556

JAJSEF5L-JULY 2012-REVISED MAY 2019

7	6	5	4	3	2	1	0
PWM_DIRECT		PS_MODE[2:0]			PWM_	FREQ[3:0]	
NAME	BIT	ACCESS	DESCRIPTION	1			
PWM_DIRECT	7	R/W	Intended for certain test mode purposes. When enabled, the entire pipeline is bypassed and PWM output is connected with PWM input.				
PS_MODE	6:4	R/W	Select PWM output phase configuration: 000 = 6-phase, 6 drivers (0°, 60°, 120°, 180°, 240°, 320°) 001 = 5-phase, 5 drivers (0°, 72°, 144°, 216°, 288°, OFF) 010 = 4-phase, 4 drivers (0°, 90°, 180°, 270°, OFF, OFF) 011 = 3-phase, 3 drivers (0°, 120°, 240°, OFF, OFF, OFF) 100 = 2-phase, 2 drivers (0°, 180°, OFF, OFF, OFF, OFF) 101 = 3-phase, 6 drivers (0°, 0°, 120°, 120°, 240°, 240°) 110 = 2-phase, 6 drivers (0°, 0°, 0°, 180°, 180°, 180°) 111 = 1-phase, 6 drivers (0°, 0°, 0°, 0°, 0°, 0°, 0°)				
PWM_FREQ	3:0	R/W	$\begin{array}{l} 0h = 4,808 \ \text{Hz} \\ 1h = 6,010 \ \text{Hz} \\ 2h = 7,212 \ \text{Hz} \\ 3h = 8,414 \ \text{Hz} \\ 4h = 9,616 \ \text{Hz} \\ 5h = 12,020 \ \text{Hz} \\ 6h = 13,222 \ \text{Hz} \\ 7h = 14,424 \ \text{Hz} \\ 8h = 15,626 \ \text{Hz} \\ 9h = 16,828 \ \text{Hz} \\ Ah = 18,030 \ \text{H} \\ Bh = 19,232 \ \text{Hz} \\ Ch = 24,040 \ \text{Hz} \\ Dh = 28,848 \ \text{Hz} \\ Fh = 33,656 \ \text{Hz} \\ Fh = 38,464 \ \text{Hz} \end{array}$	(10-bit) (10-bit) (10-bit) (10-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (8-bit) z (8-bit) z (8-bit) z (8-bit)			

#### LP8556 JAJSEF5L-JULY 2012-REVISED MAY 2019

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## 8.6.2.12 CFG6

Address A6h

CFG6 REGISTER									
7	6	5	4 3 2 1 0						
BOOST_FREQ[	1:0]		VBOOST[5:0]						
NAME	BIT	ACCESS	ACCESS DESCRIPTION						
BOOST_FREQ	7:6	R/W	Set boost switching frequency when BOOST_FSET_EN = 0. 00 = 312 kHz 01 = 625 kHz 10 = 1250 kHz 11 = undefined						
VBOOST	5:0	R/W	Boost output ve initial voltage.	oltage. When A	ADAPTIVE = 1, 1	this is the boost	minimum and		

#### 8.6.2.13 CFG7

Address A7h

CFG7 REGISTER							
7	6	5	4 3 2 1 0				0
RESERVED		EN_DRV3	EN_DRV2	RESE	RVED	IBOOS	ST_LIM[1:0]
NAME	BIT	ACCESS	DESCRIPTION				
RESERVED	7:6						
EN_DRV3	5	R/W	Selects boost more detail. 0 = Driver3 dis 1 = Driver3 en		o set boost slev	w rate. See EM	I Reduction for
EN_DRV2	4	R/W	Selects boost driver strength to set boost slew rate. See <i>EMI Reduction</i> for more detail. 0 = Driver2 disabled 1 = Driver2 enabled				
RESERVED	3:2	R/W					
IBOOST_LIM	1:0	R/W	Select boost inductor current limit (IBOOST_LIM_2X = 0 / IBOOST_LIM_2X = 1) 00 = 0.9 A / 1.6 A 01 = 1.2 A / 2.1 A 10 = 1.5 A / 2.6 A 11 = 1.8 A / not permitted				



#### 8.6.2.14 CFG9

Address A9h

CFG9 REGISTER							
7	6	5	4	3	2	1	0
VBOO	ST_MAX[2:0]		JUMP_EN	JUMP_THR	ESHOLD[1:0]	JUMP_V	OLTAGE[1:0]
NAME	BIT	ACCESS	DESCRIPTION	N			
VBOOST_MAX	7:5	R/W	Select the maximum boost voltage (typ values) (VBOOST_RANGE = 0 / VBOOST_RANGE = 1) 010 = NA / 21 V 011 = NA / 25 V 100 = 21 V / 30 V 101 = 25 V / 34.5 V 110 = 30 V / 39 V 111 = 34 V / 43 V				
JUMP_EN	4	R/W	Enable JUMP detection on the PWM input.				
JUMP_THRESHOLD	3:2	R/W	Select JUMP threshold: 00 = 10% 01 = 30% 10 = 50% 11 = 70%				
JUMP_VOLTAGE	1:0	R/W	$ \begin{array}{c} 11 = 70\% \\ \text{Select JUMP voltage:} \\ 00 = 0.5 \ V \\ 01 = 1 \ V \\ 10 = -2 \ V \end{array} $				

10 = 2 V 11 = 4 V

## 8.6.2.15 CFGA

Address AAh

CFGA REGISTER							
7	6	5	4	3	2	1	0
SSCLK_EN	RESERVED	RESE	RVED	ADAPTIVE	D	RIVER_HEADR	OOM[2:0]
NAME	BIT	ACCESS	DESCRIPTIC	DN			
SSCLK_EN	7	R/W	Enable sprea	d spectrum fund	ction		
RESERVED	6	R/W					
RESERVED	5:4	R/W					
ADAPTIVE	3	R/W	Enable adaptive boost control				
DRIVER_HEADROOM	2:0	R/W	LED driver headroom control. This sets the LOW comparator threshold and contributes to the MID comparator threshold. 000 = HEADROOM_OFFSET + 875 mV 001 = HEADROOM_OFFSET + 750 mV 010 = HEADROOM_OFFSET + 625 mV 011 = HEADROOM_OFFSET + 500 mV 100 = HEADROOM_OFFSET + 375 mV 101 = HEADROOM_OFFSET + 250 mV 110 = HEADROOM_OFFSET + 125 mV 111 = HEADROOM_OFFSET mV				

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#### LP8556 JAJSEF5L-JULY 2012-REVISED MAY 2019

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## 8.6.2.16 CFGE

Address AEh

\_ \_ \_ \_ \_ \_

CFGE REGISTER							
7	6	5	4	3	2	1	0
STEP_UP[1:0]		STEP_I	DN[1:0]	LED_FAU	_T_TH[2:0]	LED_COM	/IP_HYST[1:0]
NAME	BIT	ACCESS	DESCRIPTIO	N			
STEP_UP	7:6	R/W	Adaptive head 00 = 105 mV 01 = 210 mV 10 = 420 mV 11 = 840 mV	lroom UP step s	size		
STEP_DN	5:4	R/W	Adaptive headroom DOWN step size 00 = 105 mV 01 = 210 mV 10 = 420 mV 11 = 840 mV				
LED_FAULT_TH	3:2	R/W	LED headroon 00 = 5 V 01 = 4 V 10 = 3 V 11 = 2 V	n fault threshold	d. This sets the	HIGH compara	tor threshold.
LED_COMP_HYST	1:0	R/W	00 = DRIVER 01 = DRIVER 10 = DRIVER	comparison hy: _HEADROOM + _HEADROOM + _HEADROOM + _HEADROOM +	⊦ 1000 mV ⊦ 750 mV ⊦ 500 mV	ets the MID con	nparator threshold.

## 8.6.2.17 CFGF

Address AFh

CFGF REGISTER							
7	6	5	4	3	2	1	0
	REVISION						
NAME	BIT	ACCESS	DESCRIPTION				
REV	7:0	R/W	EPROM Settings Revision ID code				



## 9 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

#### 9.1.1 Using LP8556 With I<sup>2</sup>C Host

#### 9.1.1.1 Setting Boost Switching and PWM Dimming Frequencies

Boost switching and PWM dimming frequencies can be set via EEPROM when  $BOOST_FSET_EN = 0$  and  $PWM_FSET_EN = 0$ . Available options are shown in Table 11 and Table 12.

#### Table 11. Configuring Boost Switching Frequency via EPROM

BOOST_FSET_EN	BOOST_FREQ[1:0]	f <sub>SW</sub> [kHz]
0	00	312
0	01	625
0	10	1250
0	11	Reserved

## Table 12. Configuring PWM Dimming Frequency via EPROM

PWM_FSET_EN	PWM_FREQ[3:0]	f <sub>PWM</sub> [Hz] (Resolution)
0	0000	4808 (11-bit)
0	0001	6010 (10-bit)
0	0010	7212 (10-bit)
0	0011	8414 (10-bit)
0	0100	9616 (10-bit)
0	0101	12020 (9-bit)
0	0110	13222 (9-bit)
0	0111	14424 (9-bit)
0	1000	15626 (9-bit)
0	1001	16828 (9-bit)
0	1010	18030 (9-bit)
0	1011	19232 (9-bit)
0	1100	24040 (8-bit)
0	1101	28848 (8-bit)
0	1110	33656 (8-bit)
0	1111	38464 (8-bit)

#### 9.1.1.2 Setting Full-Scale LED Current

The LED current per output is configured by programming the CURRENT\_MAX and CURRENT registers when ISET\_EN = 0. Available options are shown below.

		0	
ISET_EN	CURRENT_MAX	CURRENT[11:0]	FULL-SCALE ILED [mA]
0	0	FFFh	5
0	1	FFFh	10
0	10	FFFh	15
0	11	FFFh	20
0	100	FFFh	23
0	101	FFFh	25
0	110	FFFh	30
0	111	FFFh	50
0	000 – 111	001h – FFFh	(CURRENT/4095) × CURRENT_IMAX

### Table 13. Setting Full-Scale LED Current with EEPROM

#### 9.1.2 Using LP8556 With Configuration Resistors and IO Pins

#### 9.1.2.1 Setting Boost Switching and PWM Dimming Frequencies

Boost switching and PWM dimming frequencies can be set via resistor when  $BOOST_FSET_EN = 1$  and  $PWM_FSET_EN = 1$ . Available options are shown in Table 14.

#### Table 14. Configuring PWM Dimming Frequency With an External Resistor

RFSET [kΩ] (TOLERANCE)	f <sub>SW</sub> [kHz] BOOST_FSET_EN = 1	f <sub>PWM</sub> [Hz] (RESOLUTION) PWM_FSET_EN = 1
Floating or FSET pin pulled HIGH	1250	9616 (10-bit)
470 k - 1 M (±5%)	312	2402 (12-bit)
300 k, 330 k (±5%)	312	4808 (11-bit)
200 k (±5%)	312	6010 (10-bit)
147 k, 150k, 154 k, 158k (±1%)	312	9616 (10-bit)
121 k (±1%)	312	12020 (9-bit)
100 k (±1%)	312	14424 (9-bit)
86.6 k (±1%)	312	16828 (9-bit)
75 k (±1%)	312	19232 (9-bit)
63.4 k (±1%)	625	2402 (12-bit)
52.3 k, 53.6 k (±1%)	625	4808 (11-bit)
44.2k, 45.3 k (±1%)	625	6010 (10-bit)
39.2 k (±1%)	625	9616 (10-bit)
34 k (±1%)	625	12020 (9-bit)
30.1k (±1%)	625	14424 (9-bit)
26.1 k (±1%)	625	16828 (9-bit)
23.2 k (±1%)	625	19232 (9-bit)
20.5 k (±1%)	1250	2402 (12-bit)
18.7 k (±1%)	1250	4808 (11-bit)
16.5k (±1%)	1250	6010 (10-bit)
14.7 k (±1%)	1250	9616 (10-bit)
13 k (±1%)	1250	12020 (9-bit)
11.8k (±1%)	1250	14424 (9-bit)
10.7 k (±1%)	1250	16828 (9-bit)
9.76 k (±1%)	1250	19232 (9-bit)
FSET pin shorted to GND	1250	Same as PWM input frequency



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#### 9.1.2.2 Setting Full-Scale LED Current

The LED current per output is configured by ISET resistor when ISET\_EN=1. In this mode the CURRENT\_IMAX and CURRENT registers can also further scale the LED current. Available options are shown in Table 15.

Table 15. Setting Full-Scale LED Curr	rent with ISET Resistor
---------------------------------------	-------------------------

RISET [Ω]	ISET_EN	CURRENT_MAX	CURRENT[11:0]	FULL-SCALE ILED [mA]
24 k	1	0	FFFh	5
24 k	1	1	FFFh	10
24 k	1	10	FFFh	15
24 k	1	11	FFFh	20
24 k	1	100	FFFh	23
24 k	1	101	FFFh	25
24 k	1	110	FFFh	30
24 k	1	111	FFFh	50
12 k – 100 k	1	000–111	001h–FFFh	(CURRENT/4095) × IMAX × 20,000 × 1.2 V / RISET

#### 9.2 Typical Application

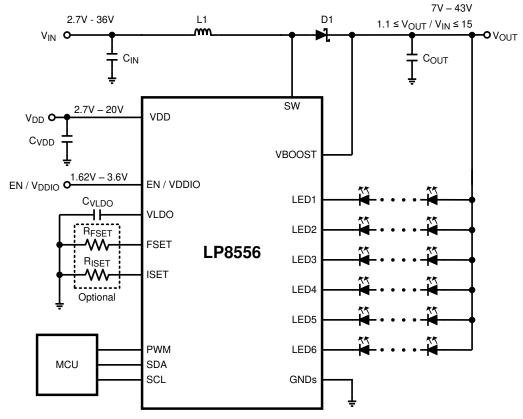


Figure 19. LP8556 Typical Application Schematic



### **Typical Application (continued)**

#### 9.2.1 Design Requirements

f <sub>sw</sub>	MIN	ТҮР	MAX	UNIT
1250	3.3		22	μΗ
625	6.8		68	μH
312	10		100	μH

#### Table 17. Recommended Output Capacitance

fsw	MIN	ТҮР	MAX	UNIT
1250	4.7			μF
625	4.7			μF
312	10			μF

#### 9.2.2 Detailed Design Procedure

#### 9.2.2.1 Recommended Inductance for the Boost Power Stage

Assumes 20 mA as the maximum LED current per string and 3.3 V as the maximum LED forward voltage.

NUMBER OF	NUMBER OF	BOOST INPUT	L1 INDUCTANCE							
LED STRINGS	LEDS PER STRING	VOLTAGE RANGE	f <sub>SW</sub> = 1250 kHz	$f_{SW}$ = 625 kHz	f <sub>SW</sub> = 312 kHz					
C	c	2.7 V - 4.4 V	3.3 μH - 6.8 μH	6.8 μH - 15 μH	10 μH - 33 μH					
0	6 6	5.4 V - 8.8 V	10 μH - 22 μH	22 μH - 47 μH	47 μΗ - 100 μΗ					
6	2	2.7 V - 4.4 V	4.7 μΗ - 10 μΗ	10 μH - 15 μH	22 μΗ - 33 μΗ					
0	8	5.4 V - 8.8 V	10 μH - 22 μH	22 μH - 68 μH	47 μH - 100 μH					
4	10	5.4 V - 8.8 V	6.8 μH - 22 μH	22 μH - 47 μH	47 μH - 100 μH					
4	12	5.4 V - 8.8 V	10 μH - 22 μH	22 μH - 47 μH	33 μΗ - 100 μΗ					

#### 9.2.2.2 Recommended Capacitances for the Boost and LDO Power Stages<sup>(1)</sup>

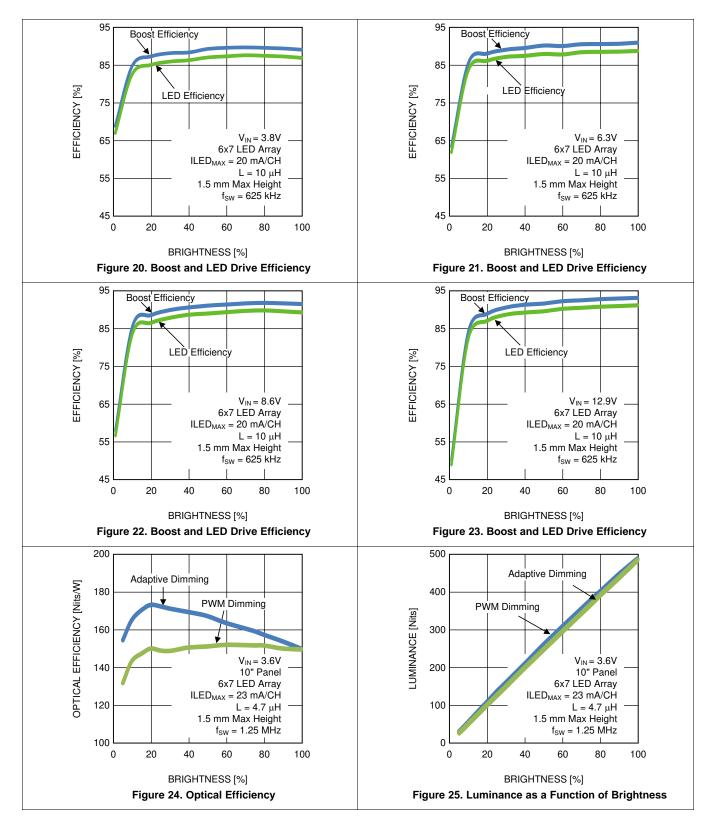
SWITCHING FREQUENCY [kHz]	C <sub>IN</sub> [μF]	C <sub>OUT</sub> [μF]	C <sub>VLDO</sub> [μF]
1250	2.2	4.7	10
625	2.2	4.7	10
312	4.7	10	10

(1) Capacitance of Multi-Layer Ceramic Capacitors (MLCC) can change significantly with the applied DC voltage. Use capacitors with good capacitance versus DC bias characteristics. In general, MLCC in bigger packages have lower capacitance de-rating than physically smaller capacitors.



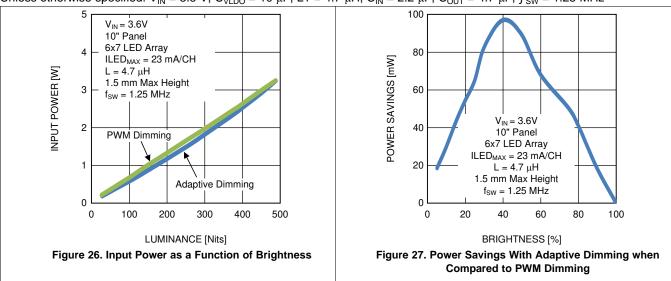
#### 9.2.3 Application Curves

Unless otherwise specified: V<sub>IN</sub> = 3.8 V,  $C_{VLDO}$  = 10  $\mu$ F, L1 = 4.7  $\mu$ H,  $C_{IN}$  = 2.2  $\mu$ F,  $C_{OUT}$  = 4.7  $\mu$ F,  $f_{SW}$  = 1.25 MHz



LP8556 JAJSEF5L-JULY 2012-REVISED MAY 2019 TEXAS INSTRUMENTS

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## **10** Power Supply Recommendations

The device is designed to operate from a VDD input voltage supply range from 2.7 V to 20 V. This input supply must be well regulated and able to withstand maximum input current and maintain stable voltage without voltage drop even at load transition condition (start-up or rapid brightness change). The resistance of the input supply rail must be low enough that the input current transient does not cause drop high enough in the LP8556 supply voltage that can cause false UVLO fault triggering.

If the input supply is located more than a few inches from the LP8556 device, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. Depending on device EEPROM configuration and usage case the boost converter is configured to operate optimally with certain input voltage range.

### 11 Layout

#### 11.1 Layout Guidelines

Figure 28 and Figure 29 follow proper layout guidelines and should be used as a guide for laying out the LP8556 circuit.

The LP8556 inductive boost converter has a high switched voltage at the SW pin, and a step current through the Schottky diode and output capacitor each switching cycle. The high switching voltage can create interference into nearby nodes due to electric field coupling ( $I = C \times dV/dt$ ). The large step current through the diode and the output capacitor can cause a large voltage spike at the SW and VBOOST pins due to parasitic inductance in the step current conducting path ( $V = L \times di/dt$ ). Board layout guidelines are geared towards minimizing this electric field coupling and conducted noise.

The following list details the main (layout sensitive) areas of the device inductive boost converter in order of decreasing importance:

- 1. Boost Output Capacitor Placement
  - Because the output capacitor is in the path of the inductor current discharge path, there is a high-current step from 0 to IPEAK each time the switch turns off and the Schottky diode turns on. Any inductance along this series path from the diodes cathode, through COUT, and back into the LP8556 GND pin contributes to voltage spikes (VSPIKE = LP\_ x dl/dt) at SW and OUT. These spikes can potentially overvoltage the SW and VBOOST pins, or feed through to GND. To avoid this, COUT+ must be connected as close to the cathode of the Schottky diode as possible, and COUT- must be connected as close to the LP8556 GND bumps as possible. The best placement for COUT is on the same layer as the LP8556 to avoid any vias that can add excessive series inductance.
- 2. Schottky Diode Placement
  - In the device boost circuit the Schottky diode is in the path of the inductor current discharge. As a result the Schottky diode has a high-current step from 0 to IPEAK each time the switch turns off and the diode turns on. Any inductance in series with the diode causes a voltage spike (VSPIKE = LP\_ × dl/dt) at SW and OUT. This can potentially over-voltage the SW pin, or feed through to VOUT and through the output capacitor, into GND. Connecting the anode of the diode as close to the SW pin as possible, and connecting the cathode of the diode as close to COUT+ as possible reduces the inductance (LP\_) and minimize these voltage spikes.
- 3. Boost Input/VDD Capacitor Placement
  - The LP8556 input capacitor filters the inductor current ripple and the internal MOSFET driver currents. The inductor current ripple can add input voltage ripple due to any series resistance in the input power path. The MOSFET driver currents can add voltage spikes on the input due to the inductance in series with the VIN/VDD and the input capacitor. Close placement of the input capacitor to the VDD pin and to the GND pin is critical because any series inductance between VIN/VDD and CIN+ or CIN– and GND can create voltage spikes that could appear on the VIN/VDD supply line and GND.
  - Close placement of the input capacitor at the input side of the inductor is also critical. The source impedance (inductance and resistance) from the input supply, along with the input capacitor of the LP8556, forms a series RLC circuit. If the output resistance from the source is low enough, the circuit is underdamped and will have a resonant frequency (typically the case).
  - Depending on the size of LS, the resonant frequency could occur below, close to, or above the switching frequency of the LP8556. This can cause the supply current ripple to be:



### Layout Guidelines (continued)

- Approximately equal to the inductor current ripple when the resonant frequency occurs well above the LP8556 switching frequency.
- Greater than the inductor current ripple when the resonant frequency occurs near the switching frequency.
- Less than the inductor current ripple when the resonant frequency occurs well below the switching frequency.

#### 11.2 Layout Examples

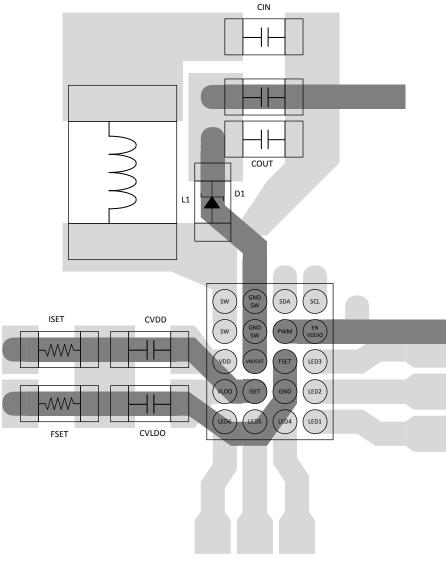
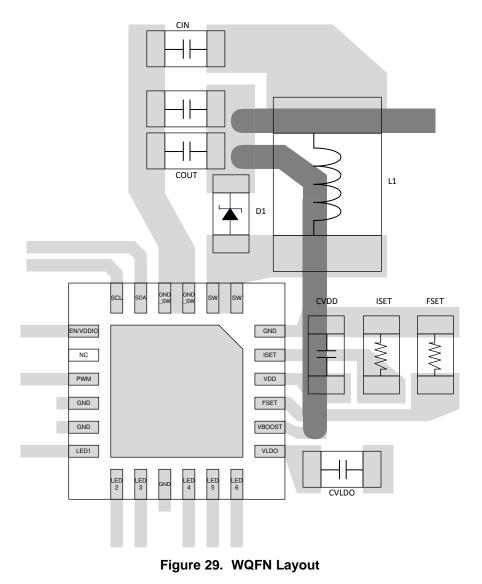


Figure 28. DSBGA Layout



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## Layout Examples (continued)





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## 12 デバイスおよびドキュメントのサポート

## 12.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

## 12.2 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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## 12.4 静電気放電に関する注意事項

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## 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスに ついて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もありま す。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。



13-Dec-2020

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LP8556SQ-E00/NOPB	ACTIVE	WQFN	RTW	24	1000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E0	Samples
LP8556SQ-E08/NOPB	ACTIVE	WQFN	RTW	24	1000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E8	Samples
LP8556SQ-E09/NOPB	ACTIVE	WQFN	RTW	24	1000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E9	Samples
LP8556SQE-E00/NOPB	ACTIVE	WQFN	RTW	24	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E0	Samples
LP8556SQE-E08/NOPB	ACTIVE	WQFN	RTW	24	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E8	Samples
LP8556SQE-E09/NOPB	ACTIVE	WQFN	RTW	24	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E9	Samples
LP8556SQX-E00/NOPB	ACTIVE	WQFN	RTW	24	4500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E0	Samples
LP8556SQX-E08/NOPB	ACTIVE	WQFN	RTW	24	4500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E8	Samples
LP8556SQX-E09/NOPB	ACTIVE	WQFN	RTW	24	4500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-30 to 85	L8556E9	Samples
LP8556TME-E02/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E2	Samples
LP8556TME-E03/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E3	Samples
LP8556TME-E04/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E4	Samples
LP8556TME-E05/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E5	Samples
LP8556TME-E06/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E6	Samples
LP8556TME-E09/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E9	Samples
LP8556TME-E11/NOPB	ACTIVE	DSBGA	YFQ	20	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	6E11	Samples
LP8556TMX-E02/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E2	Samples
LP8556TMX-E03/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E3	Samples
LP8556TMX-E04/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E4	Samples
LP8556TMX-E05/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E5	Samples



13-Dec-2020

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LP8556TMX-E06/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E6	Samples
LP8556TMX-E09/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	56E9	Samples
LP8556TMX-E11/NOPB	ACTIVE	DSBGA	YFQ	20	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-30 to 85	6E11	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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Texas

STRUMENTS

## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal					<b>.</b>	(						r
Device	Package Type	Package Drawing		SPQ	Reel Diameter		A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
					(mm)	W1 (mm)						
LP8556SQ-E00/NOPB	WQFN	RTW	24	1000	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQ-E00/NOPB	WQFN	RTW	24	1000	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQ-E08/NOPB	WQFN	RTW	24	1000	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQ-E08/NOPB	WQFN	RTW	24	1000	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQ-E09/NOPB	WQFN	RTW	24	1000	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQ-E09/NOPB	WQFN	RTW	24	1000	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQE-E00/NOPB	WQFN	RTW	24	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQE-E00/NOPB	WQFN	RTW	24	250	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQE-E08/NOPB	WQFN	RTW	24	250	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQE-E08/NOPB	WQFN	RTW	24	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQE-E09/NOPB	WQFN	RTW	24	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQE-E09/NOPB	WQFN	RTW	24	250	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQX-E00/NOPB	WQFN	RTW	24	4500	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQX-E00/NOPB	WQFN	RTW	24	4500	330.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556SQX-E08/NOPB	WQFN	RTW	24	4500	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQX-E08/NOPB	WQFN	RTW	24	4500	330.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1

# PACKAGE MATERIALS INFORMATION



www.ti.com

26-Oct-2024

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LP8556SQX-E09/NOPB	WQFN	RTW	24	4500	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q1
LP8556SQX-E09/NOPB	WQFN	RTW	24	4500	330.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LP8556TME-E02/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TME-E03/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TME-E04/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TME-E05/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TME-E06/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TME-E09/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TME-E11/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E02/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E03/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E04/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E05/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E06/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E09/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1
LP8556TMX-E11/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1



# PACKAGE MATERIALS INFORMATION

26-Oct-2024



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LP8556SQ-E00/NOPB	WQFN	RTW	24	1000	208.0	191.0	35.0
LP8556SQ-E00/NOPB	WQFN	RTW	24	1000	210.0	185.0	35.0
LP8556SQ-E08/NOPB	WQFN	RTW	24	1000	210.0	185.0	35.0
LP8556SQ-E08/NOPB	WQFN	RTW	24	1000	208.0	191.0	35.0
LP8556SQ-E09/NOPB	WQFN	RTW	24	1000	208.0	191.0	35.0
LP8556SQ-E09/NOPB	WQFN	RTW	24	1000	210.0	185.0	35.0
LP8556SQE-E00/NOPB	WQFN	RTW	24	250	210.0	185.0	35.0
LP8556SQE-E00/NOPB	WQFN	RTW	24	250	208.0	191.0	35.0
LP8556SQE-E08/NOPB	WQFN	RTW	24	250	208.0	191.0	35.0
LP8556SQE-E08/NOPB	WQFN	RTW	24	250	210.0	185.0	35.0
LP8556SQE-E09/NOPB	WQFN	RTW	24	250	210.0	185.0	35.0
LP8556SQE-E09/NOPB	WQFN	RTW	24	250	208.0	191.0	35.0
LP8556SQX-E00/NOPB	WQFN	RTW	24	4500	367.0	367.0	35.0
LP8556SQX-E00/NOPB	WQFN	RTW	24	4500	367.0	367.0	35.0
LP8556SQX-E08/NOPB	WQFN	RTW	24	4500	367.0	367.0	35.0
LP8556SQX-E08/NOPB	WQFN	RTW	24	4500	367.0	367.0	35.0
LP8556SQX-E09/NOPB	WQFN	RTW	24	4500	367.0	367.0	35.0
LP8556SQX-E09/NOPB	WQFN	RTW	24	4500	367.0	367.0	35.0

# PACKAGE MATERIALS INFORMATION

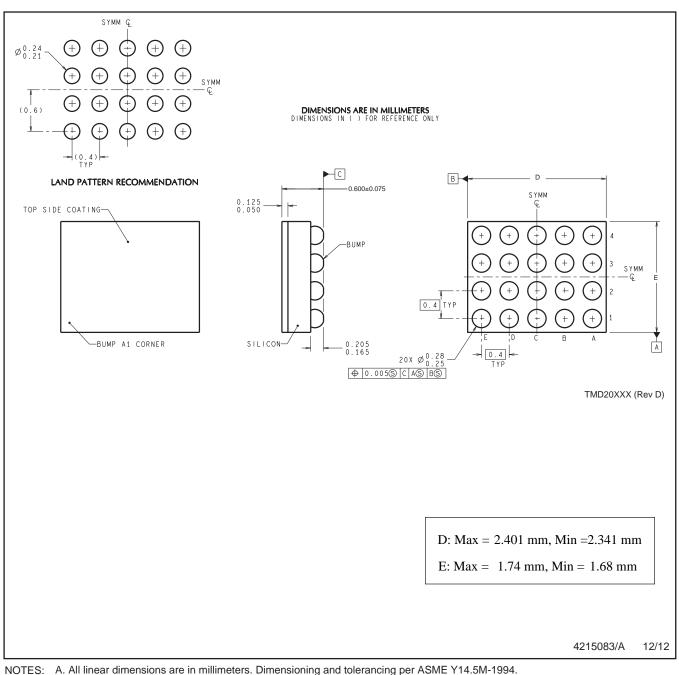


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26-Oct-2024

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LP8556TME-E02/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TME-E03/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TME-E04/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TME-E05/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TME-E06/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TME-E09/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TME-E11/NOPB	DSBGA	YFQ	20	250	208.0	191.0	35.0
LP8556TMX-E02/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0
LP8556TMX-E03/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0
LP8556TMX-E04/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0
LP8556TMX-E05/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0
LP8556TMX-E06/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0
LP8556TMX-E09/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0
LP8556TMX-E11/NOPB	DSBGA	YFQ	20	3000	208.0	191.0	35.0

# YFQ0020



B. This drawing is subject to change without notice.



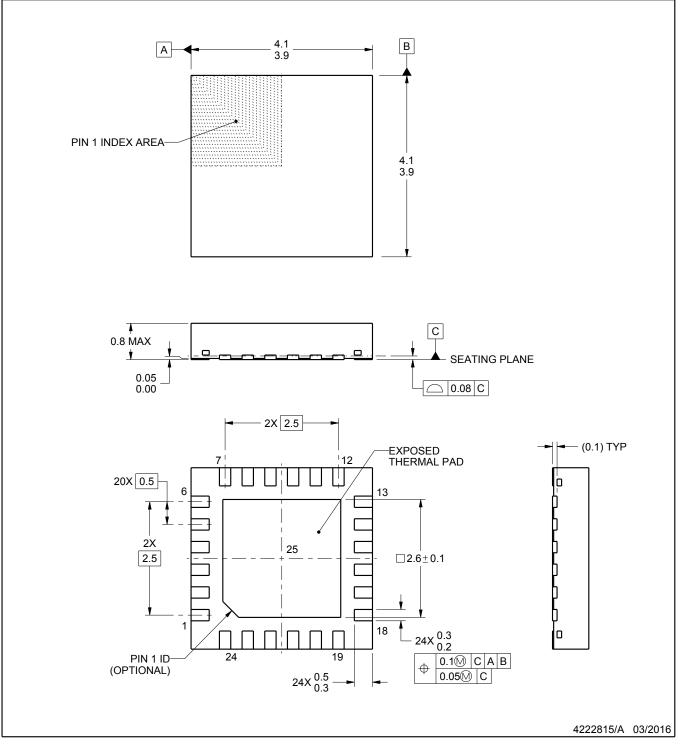
# **RTW0024A**



# **PACKAGE OUTLINE**

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

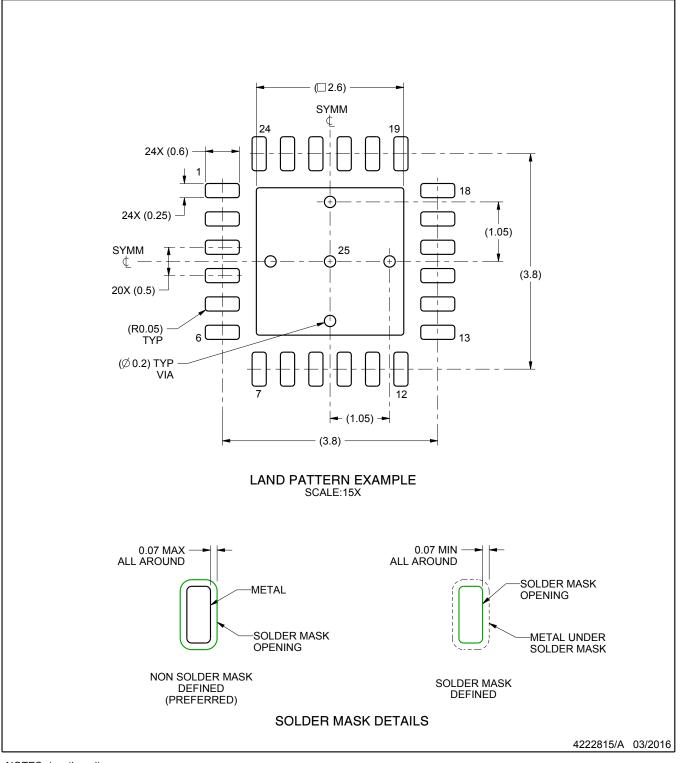


# **RTW0024A**

# **EXAMPLE BOARD LAYOUT**

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

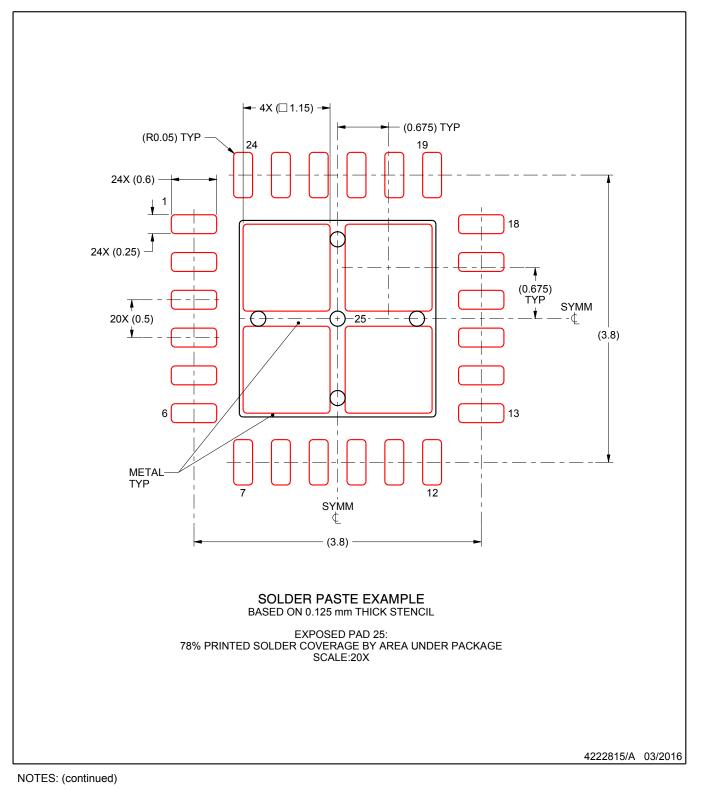


# **RTW0024A**

# **EXAMPLE STENCIL DESIGN**

## WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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